VLBA Technical Report No. 7 (Rev. C)

LO TRANSMITTER MODULE (L102) and LO RECEIVER MODULE (L105).

A. R. Thompson Feb. 10, 1993

Design Changes and Retrofits.

The LO System underwent several changes in design during the construction phase of the VLBA electronics. In the current version described in this manual the 500 MHz reference is sent out to the antenna at 500,000 MHz. i.e. without any frequency offset. At the antenna the VCXO is locked without an IF in the loop. In an earlier version the 500 MHz transmitted to the antenna was offset by 2.083 kHz. The VCXO at the antenna was locked with a loop IF of 2.083 kHz and the offset was thereby removed from the output of the LO Transmitter module. This arrangement offered some advantage in a particular implementation of the pulse calibration system, but was abandoned when it was found that it was difficult to suppress residual sidebands at the offset frequency. Monitor detector amplifiers in modules with serial numbers one through six initially had a standard output of one volt positive, rather than one volt negative. In the Round-Trip Monitor module, which is also part of the LO system but is not described in this manual, the averaging time for the round trip phase measurement was 1 second in early units but was later increased to 3 seconds. Retrofits have been made to bring all LO modules into conformity with the system described in this manual.

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FIGURES

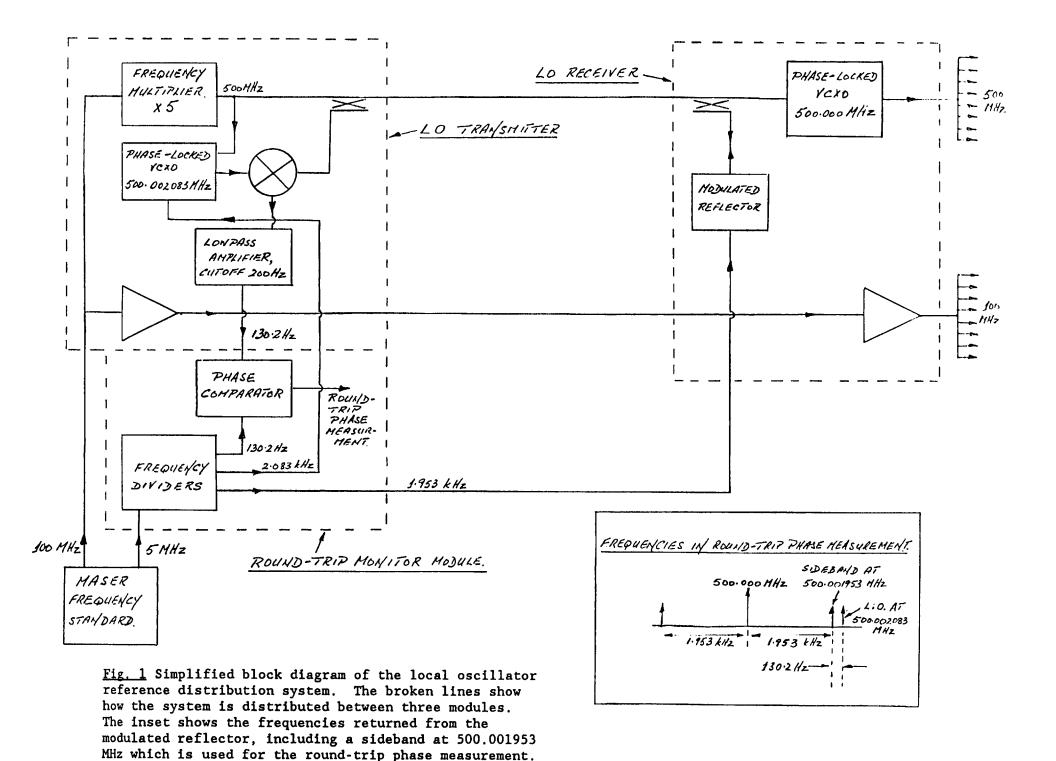
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(1) Basic Description of the Local Oscillator Reference System.

The purpose of the system described in this manual is to provide a high stability reference frequency at the antenna that can be multiplied as necessary to obtain the required local oscillator signals. The transmission line that caries this signal from the electronics building to the antenna vertex room is approximately 70 m long, and must be monitored by a round-trip phase measurement. In selecting the reference frequency it is important that it should be high enough that the line length can be monitored with sufficient accuracy. On the other hand it should be low enough that the discrete tuning steps in the LO frequencies are not too widely separated, that the loss in the transmission line is not too high, and that good matching can be maintained. It is also useful if the frequency is within the range for which voltagecontrolled crystal oscillators are available. These considerations led to a choice of 500 MHz. The goal is to transmit this frequency to the antenna without degradation, so that the phase stability is determined mainly by the maser from which the signal is derived. A frequency of 100 MHz is also transmitted to the antennas to provide a reference for the phase-locked loop in the 2-16 GHz Synthesizer modules. Since this is not multiplied in frequency, the phase stability requirement is not so high.

A simplified block diagram of the system is shown in Fig. 1, in which the broken lines indicate the distribution into three modules. Two of these are located in the electronics building at each site, and one in the antenna vertex room. A frequency of 100 MHz is supplied by the maser, and this is frequency multiplied to 500 MHz, and transmitted to the antenna. It is also used to lock a voltage-controlled crystal oscillator (VCXO) with an offset of 2.083 kHz which is used in the round-trip phase measurement. A frequency of 100 MHz is also transmitted directly to the antenna. The signals at 100 and 500 MHz could be carried on the same cable, but separate cables have been used to avoid the need for diplexing filters.

To implement the round-trip phase measurement a small part of the 500 MHz signal at the antenna is reflected back down the cable by a diode reflector that is driven between on and off states by a squarewave at 1.953 kHz. returned signal thus contains sidebands at (500.000000 ± 0.001953) MHz: see Fig. 1 (inset). At the maser location the returned signals are converted with the local oscillator at 500.002083 MHz, and the upper sideband then appears as a signal at 130.2 Hz from the output of the mixer. This signal is separated from other signals from the mixer by means of a lowpass filter with cutoff at 200 MHz, and its phase is compared with that of a locally generated 130.2 Hz signal to provide the round-trip phase measurement. Note that the strongest signal entering the R-port of the mixer is likely to be the 500.000 MHz reflected from mismatches in the cable, and not the component from the modulated reflector. Since the cable contains flexible sections that bend as the antennas slew and track, such a component will vary with time in both amplitude and phase. With the scheme in Fig. 1, the wanted output at 130.2 Hz is generated by the combination of two frequencies which do not include 500.000 MHz, so that a component at this last frequency on one port of the mixer has no effect on the wanted output. Thus the possibility of an unwanted reflection causing phase errors in the round trip measurement is avoided.



Note that a VCXO is required at the antenna to remove any vestiges of the reflector modulation frequency. Although the reflected component is launched onto the transmission line in the direction of the transmitter module, reflections in the line will produce components travelling towards the receiver which appear as low level sidebands on the wanted reference frequency. The 500 MHz reference at the output of the LO transmitter must be free from noise or other sidebands to a high degree, since to provide the required LO signals it will be multiplied by factors up to 170 (for 86 GHz), resulting in enhancement of sidebands by up to 45 dB. Thus a VCXO is necessary to eliminate such sidebands.

The Round-Trip Monitor module is described in a separate report by Erich Schlecht, but it may be useful to give a few details here. The three low frequencies are generated from a 1 MHz signal derived from the 5 MHz output of the maser by frequency division as follows:

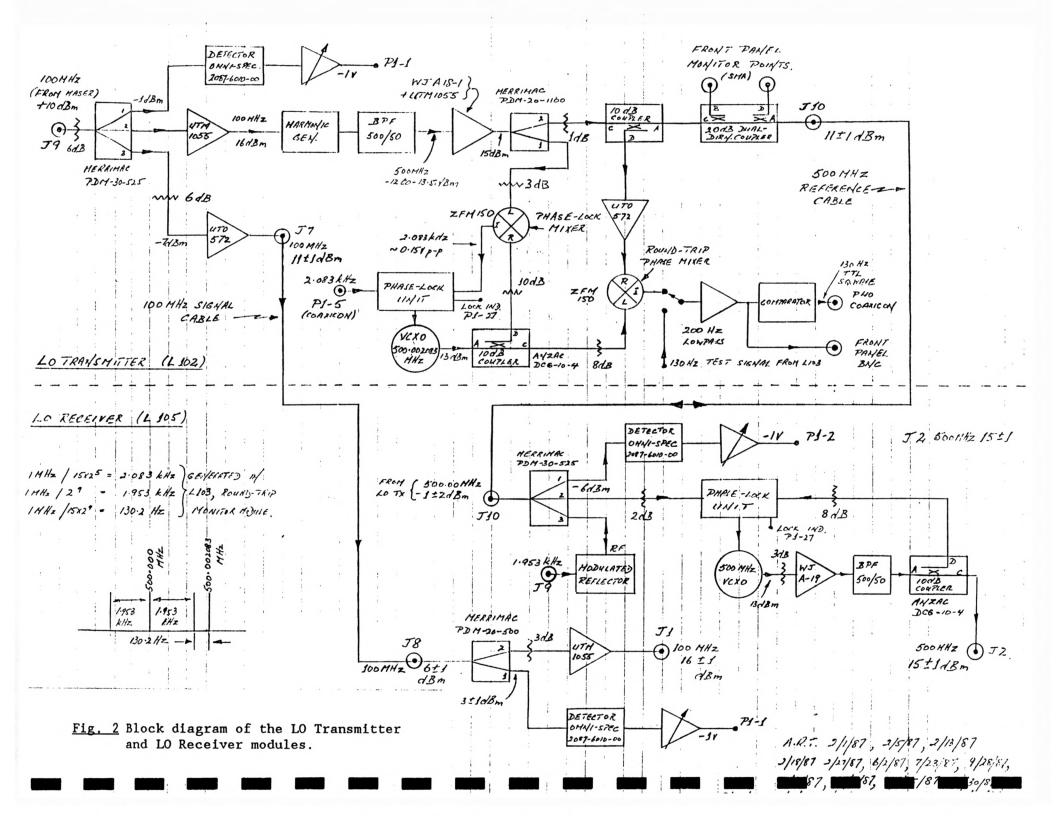
- 2.083 kHz = 1 MHz / 15 x 2**5
- 1.953 kHz = 1 MHz / 2**9
- 130.2 Hz = 1 MHz / 15 x 2**9

Synchronous counters are used. All three frequencies contain at least one division by two, which is necessary to obtain symmetrical squarewave outputs. In addition it is necessary that the frequency used in the phase measurement (130.2 Hz) be obtained by a division by four, since two reference waveforms in phase quadrature are used in the phase comparison. The counter chains are reset to zero every three seconds as a precaution against possible disturbance of their relative phases by, for example, a transient power failure. Three seconds is the shortest integral number of seconds that contains an integral number of cycles at 2.083 kHz, and thus zeroing every three seconds avoids introducing phase jumps in the 2.083 kHz which would disturb the phase-locked loops. The phase comparison is done by gateing and counting 5 MHz pulses, and the counters used here are also read out and reset at the same three second intervals. The count data are read out through a monitor and control interface card in the module.

(2) Design of the LO Transmitter Module.

A detailed block diagram of the LO Transmitter module is shown in the top half of Fig. 2. A 100 MHz input to the module is split three ways. The first output of the splitter goes to a level monitoring detector (Omni Spectra 20090), the output of which is amplified to a standard value of -1 volt when the 100 MHz input level is correct. A circuit diagram of the amplifier is

¹ An alternative series of frequencies that would allow readouts at any multiple of 50 milliseconds would be obtained by dividing 1 MHz by $(5**3)\times(2**2)$, $(2**5)\times3\times5$, and $(2**5)\times3\times(5**3)$ to obtain 2.083 kHz, 2.000 kHz, and 83.3 Hz, respectively, and using 2.000 kHz as the offset frequency for the 500 MHz transmitted to the antenna. The divider chains would require slightly more IC's than are used in the present scheme.



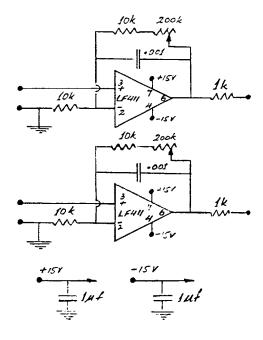
shown in Fig. 3. The amplifier circuit board includes two of these amplifiers, only one of which is used in the LO Transmitter, but both are used in the LO Receiver. The third output from the power splitter is amplified and goes to the LO Receiver.

The second output of the splitter goes to a harmonic generator to produce 500 MHz. The generator uses a design by R. Mauzy, and is shown in Fig. 4. The 500 MHz is then split and one output goes through a cable to the LO Receiver in the antenna. Before leaving the LO Transmitter it passes through a dual directional coupler with outputs on the module front panel. This coupler is included to monitor the signals on the cable. The other 500 MHz signal is used to drive the L-port of the phase-lock mixer at a nominal level of 10 dBm. Note that this level is not critical, and a range of 7 to 13 dBm is satisfactory. The phase-lock mixer is used in the phase locked loop that locks the VCXO at 500.002083 MHz. A description of the circuitry in the phase lock unit is given in the section that follows. The signals returned down the 500 MHz line from the modulated reflector are sampled by a 10-dB coupler and fed through an amplifier to the round-trip phase mixer. Note that the amplifier provides isolation to prevent signals at 500.002083 Mhz that leak through the mixer from contaminating the outgoing 500 MHz. The signal from the I-port of the mixer contains the required 130.2 Hz component which is selected out by a 200 Hz lowpass amplifier, and then turned into a TTL squarewave by a comparator. A block diagram of the amplifier and comparator is shown in Fig. 5. The squarewave from the comparator goes to the Round-Trip Monitor module (L103). A switch at the input of the lowpass amplifier allows for connection to a 130.2 Hz reference waveform from the Round-Trip Monitor module for test purposes, including checking of the phase stability of the lowpass amplifier.

(3) The LO-Transmitter Phase Lock Unit.

A circuit diagram of the unit is given in Fig. 6. A digital phase detector type MC4044, U6 in the diagram, receives inputs at 2.083 kHz on pins 1 and 3. One of these is the beat frequency between the high frequency reference and the VCXO frequency that comes from the I-port of the phase-lock mixer, and the other is a TTL-level squarewave at 2.083 kHz that is generated in the Round-Trip Monitor module. The output of the MC4044 (pins 5 and 10) feeds an integrating amplifier, LH0022 (U7), the output of which goes to the frequency control of the VCXO via a buffer amplifier (U10). The output of the MC4044 varies over a range of approximately 0.8 to 2.1 volts as the relative phase on its inputs varies. Pin 12 of the LH0022 is held at 1.5 volts, and the action of the loop drives the MC4044 to equalize the input voltages of the LH0042.

The two inputs to the phase detector can be transposed by means of jumper wires on the circuit board to obtain high or low lock, i.e. the VCXO locked at 2.083 kHz higher or lower than the high frequency reference at the phase lock mixer, respectively. High lock is used in the LO Transmitter, but in an earlier version of the LO Receiver this phase lock unit was used in the low-lock mode.



 $\underline{\text{Fig. 3}}$ Amplifier circuits for the outputs of the level-monitoring detectors. The 200k trimpots allow the outputs to be set to a standard value of -1 volt when the monitored signal has the desired level.

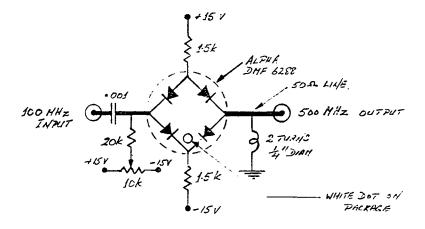
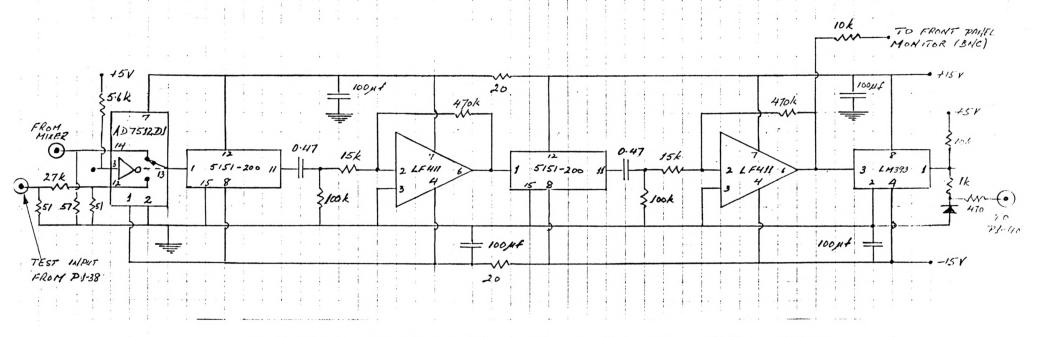
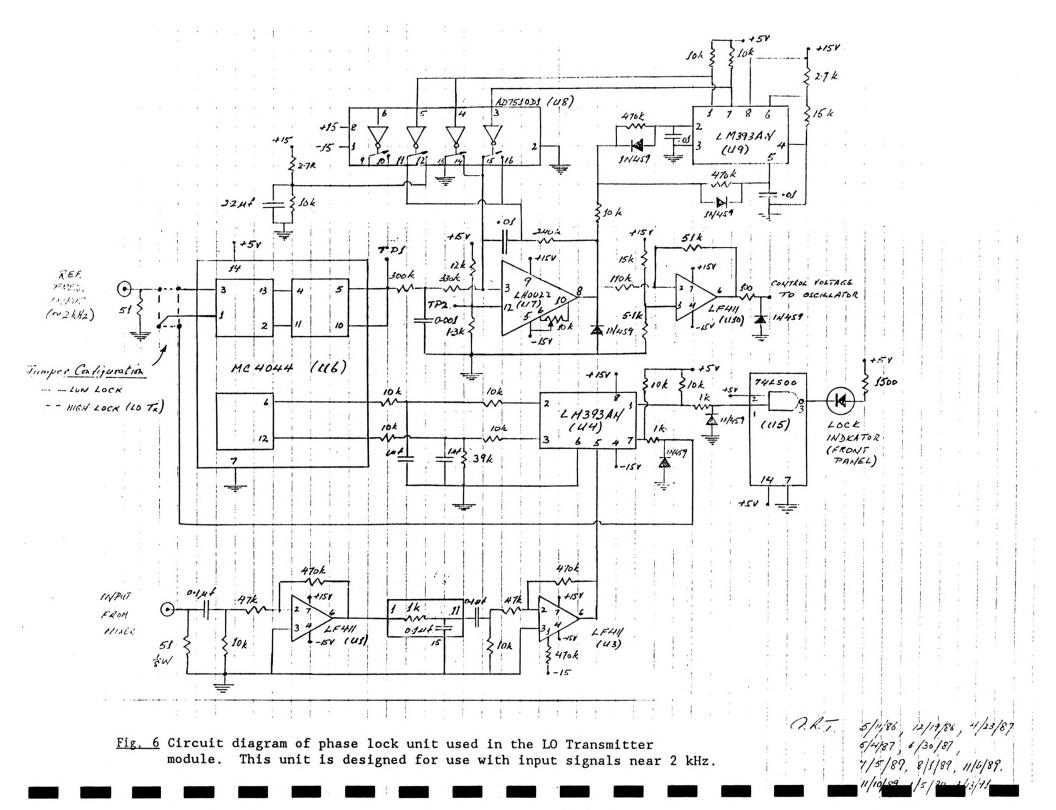


Fig. 4 X5 Multiplier circuit. The 10k trimpot is adjusted to minimize the amplitude of even-order harmonics in the output.



 $\frac{\text{Fig. 5}}{\text{two active lowpass filter units with cutoff frequency 200 Hz.}}$

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The input from the phase-lock mixer is amplified in a lowpass amplifier consisting of two LF411 IC's (Ul and U3). As initially designed a 5151-2500 lowpass active filter (U2) with cutoff at 2.5 kHz was also included, but it was found to be better to replace this with a single RC time constant (1k and 0.1 μ f) mounted on a dip header. In order to use the frequency discriminator action of the MC4044 to cause the loop to move into lock, the amplifier must pass the beat frequency from the mixer for any frequency within the tuning range of the VCXO. The single pole response allows this. The output signal from the LF411 stages goes to pin 5 of the LM393AN comparator (U4) which produces a TTL squarewave to drive the MC4044. The MC4044 also serves as a lock detector, and drives input pins 2 and 3 of comparator U4. When the loop is locked, pin 3 is positive with respect to pin 2, and when the loop is unlocked it is negative.

The MC4044 acts as a frequency comparator as well as a phase detector. Thus when the system is first switched on the LH0022 integrator should slew the VCXO into lock. In the case of the high-lock configuration, the system will go directly into lock so long as the VCXO frequency is higher than the 500 MHz reference at the phase-lock mixer. If the system happens to come up with the VCXO lower than the reference, the frequency comparator action will slew the VCXO away from lock until the LH0022 reaches the end of its range. (In the low-lock case the corresponding problem arises if the VCXO comes up at a higher frequency than the reference.) The solution is to detect when the integrator hits one end of its range and then make it jump to the other end, from which it will go straight into lock. This is accomplished using the comparator U9 and the FET switches AD7510D1 (U8). If the integrator output on pin 5 of U9 exceeds the 13 volts on pin 6, the switch at pins 15-16 of U8 closes and discharges the integrating capacitor $(0.01 \mu f)$, causing the integrator output to fall to zero. If the output of the integrator on pin 2 of U9 goes below zero volts, the switches at pins 11-12 and 13-14 of the AD7510Dl both close charging the integrating capacitor up to 12 volts, and thus causing the integrator output to jump to the same value. Note that the connections from pin 8 of the LH0022 to pins 2 and 5 of U9 each contain 470k in parallel with a diode. This arrangement allows the comparator to follow the slewing of the LH0022 with a short time constant, but presents a longer time constant when the LH0022 jumps across its range, in order to give adequate time for the integrating capacitor to charge or discharge. If the lock is broken by removing one of the reference signals, the LH0022 will sweep across its range and jump back repetitively, producing a sawtooth waveform. The sweep period is usually about 100 msec, but both the direction and rate of the sweep depend upon the voltage from the MC4044, which in turn depends upon what the inputs to that IC happen to be. The loop will automatically go into lock as soon as the lock conditions are restored.

The components that determine the response of the loop are shown in Fig. 7. The MC4044 gain constant (phase sensitivity) is 0.12 volts/radian. The tuning sensitivity of the VCXO, Vectron CO-283VW-OR, is 8 kHz/volt at the oscillator terminal, but in the loop it is effectively 3.7 kHz/volt since it is fed through the buffer stage, UlO, with voltage gain 0.46. The buffer is inserted to reduce the voltage range applied to the oscillator to approximately 0 - 6 volts. With these parameters and the R and C values in Fig. 7, the natural frequency of the loop is 104 Hz and the damping factor is 0.79.

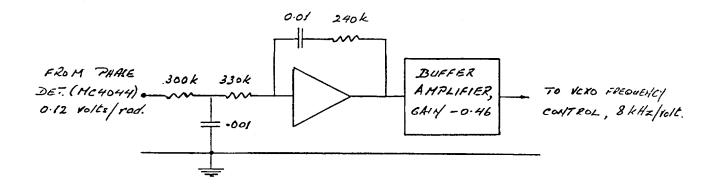


Fig. 7 Parameter values that determine the bandwidth and damping characteristics of the LO Transmitter phase-locked loop.

(4) Inputs and Outputs of the LO Transmitter.

OSP Connectors, Rear Panel

- J7 100 MHz output
- J9 100 MHz input
- J10 500.000 MHz output

42-Pin AMP Connector, Rear Panel

- 1 Monitor detector level for 100 MHz
- 5 (coaxicon) 2.08 kHz input
- 10 +5 volts input
- 16 +15 volts input
- 17 -15 volts input
- 25 130 Hz amplifier input switch control, TTL high for input from mixer and TTL low for test signal
- 27 Lock indicator, TTL low for loop in lock
- 34 Ground
- 38 (coaxicon) 130 Hz test signal input
- 40 (coaxicon) 130 Hz output from amplifier and comparator unit
- 42 Ground

Front Panel

- BNC Output waveform of 130 Hz amplifier
- LED Lock indicator, on for loop in lock
- SMA connectors, coupled arm of directional coupler to monitor signals in 500 MHz line

(5) Checkout of the LO Transmitter.

The following procedure refers to checkout of the module on the bench. Further checkout of the overall function, in particular the measurement of round trip phase, should be made with the module in the rack. Refer to the LO Transmitter block diagram in the upper half of Fig. 2. Apply a 100 MHz signal at 10 dBm level to the J9 OSP connector.

- (1) Check the output of the monitoring detector and set the gain of the amplifier that it drives to provide -1 volt at pin 1 of the 42-pin connector for 10 dBm input at 100 MHz.
- (2) Check the 100 MHz output at J7 OSP connector. It should be 11 ± 1 dBm. The second harmonic at this point should be about 23 dB below the 100 MHz level. If necessary adjust the attenuator at the input of the three-way power splitter, or the attenuator at output 3 of the splitter.
- (3) Remove the 500/50 MHz filter at the output of the harmonic generator and monitor the output at this point with a spectrum analyzer. The amplitudes of the even harmonics of 100 MHz can be varied by adjusting the potentiometer on the board in the harmonic generator box. Adjust to

minimize the levels of the 400 and 600 MHz harmonics. The level at 500 MHz should be -12 to -13.5 dBm. If necessary, adjust the attenuator at the input of the three-way power splitter and repeat check (2).

- (4) At the output of the two-way power splitter for the 500 MHz signal the 500 MHz level should be 11-12 dBm. The second harmonic at 1 GHz should be about 28 dB down, and the other harmonics of 100 MHz should be at least 50 dB down. The output level at OSP connector J10 should be 11 ± 1 dBm.
- (5) Check the input waveform to the phase-lock unit from the I-port of the phase-lock mixer. It should be 0.05-0.15 volts p-p, and will not be a clean sine wave because the VCXO should be sweeping in frequency. The output of the module at OSP connector J10 should be terminated for this measurement.
- (6) Adjust the phase-lock unit following the steps described below. Refer to the circuit diagram in Fig. 6.
 - (a) Remove IC's MC4044 and AD7510 from the board and connect test point TP1 (pins 5 and 10 of MC4044) to TP2 (pin 12 of LH0022). Monitor pin 6 of LF411 with an oscilloscope or test meter. The voltage at this point can be made to slew both positive and negative by adjustment of the offset pot for the LH0022. The pot should be set so that the voltage can be held steady (drift rate no more than, say, 0.1 volt in 30 sec.) near 2 volts, which is close to the output to the VCXO frequency control when the loop is in lock. Replace IC's.
 - (b) Check the waveform at the frequency control terminal of the VCXO. The voltage should sweep repetitively between -0.5 and 5.5 volts (\pm 0.5 volts) with a period of about 100 msec. Pin 8 of the LH0022 similarly sweeps between approximately 2 and 13 volts.
 - (c) Apply to pin 5 of the 42-pin Amp connector a TTL-level squarewave at 2 kHz frequency from a manually variable source. The loop should lock. The lock condition can be verified by varying the 2 kHz input frequency and noting the corresponding variation in the input waveform from the phase-lock mixer, or the variation of the VCXO control voltage. Note that it is useful to display the phase-lock mixer waveform and the 2 kHz TTL reference on two traces of an oscilloscope, with the sweep locked to the latter waveform. The mixer waveform should have a good sine wave shape with no obvious harmonic distortion or phase jitter. If there is jitter, it may be due to the RF reference input to the module at 100 MHz or 500 MHz, especially if a synthesized signal generator is being used. In tests in Charlottesville, a crystal oscillator was found to provide a more stable reference.
 - (d) In case of failure to lock, check the action of the phase detector as follows. Connect the frequency control terminal of the VCXO to a source of about 1.5 volts, and adjust this so that the output of the phase-lock mixer is a sine wave of frequency approximately 2 kHz. A squarewave version of this frequency appears at the MC4044, on pin 3 in an LO Tx or pin 1 in an LO Rx. The reference from the 2-kHz source will appear on the other pin of the pin-1/pin-3 pair. Monitor the output of

the MC4044 at TP1 with an oscilloscope. The waveform is complicated, but the mean voltage should be approximately 2.1 when the frequency on pin 3 is greater than that on pin 1, and 0.8 when this condition is reversed. The voltage on TP2 should be intermediate between these two values.

- (e) Check the operation of the lock detector. The lock detector senses the relative voltage of pins 6 and 12 of the MC4044. Monitor these voltages at pins 2 and 3 of the comparator U4. With the loop locked, pin 3 should be about 1 volt positive with respect to pin 2, and with the loop unlocked it should be negative. If one or both of the 100 MHz and 2 kHz inputs to the module have been removed to obtain the unlocked condition, this will affect the measured voltage.
- (f) If the 100 MHz is being supplied by a synthesized signal generator, run the frequency up and down in 0.1 kHz steps. The loop should typically stay in lock over a range of -2 to +3.5 kHz of the 100 MHz, i.e. -10 to +17.5 kHz variation of the 500 MHz reference input to the phase-lock mixer. It is useful to display the VCXO control voltage on an oscilloscope during this check.
- (g) On U3 (LF411) in Fig. 6 the purpose of the 470k resistor to -15 volts from pin 1 is to make the output of the amplifier slightly negative (about 20 mv) when there is no input from the phase lock mixer. The output at pin 7 of comparator U4 is then TTL low, rather than indeterminate as it would be with zero output from U3. A TTL high on pin 7 of U4 with no signal from the phase lock mixer could cause the lock detector to give a false indication of lock. Check the U3 output level with no signal by removing the DIP header in the amplifier chain.
- (7) Checkout of 130 Hz amplifier and comparator. Refer to Fig. 5 for the circuit diagram. The gain of the amplifier should be checked. At 130 Hz the voltage gain factor from the input terminal to pin 3 on the LM393 comparator should be in the range 800-1000. The lowpass response should have reduced the voltage gain by a factor of approximately 2 at 210 Hz and approximately 10 at 280 Hz. Pin 25 of the 42-pin connector should be high or open to connect the input of the amplifier to the signal input connector on the amplifier box.

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(6) List of Drawings, Artwork, and Bills of Materials for LO Transmitter.

Schematic and Logic Diagrams	
Phase Lock Circuit for 2 kHz Reference	B53304S002 Rev F
130 Hz Amplifier and Comparator	B53304S004
X5 Multiplier	A53304S005
Monitor Detector Amplifiers	A53304S006 Rev A
2-Stage 500 MHz Amplifier	A53304S008
Bills of Materials	
L102 Module	A53304B003*
Phase Lock Unit for 2 kHz Reference	A53304B002
130 Hz Amplifier and Comparator	A53304B004

X5 Multiplier

Monitor Detector Amplifier Board	A53304B006		
2-Stage 500 MHz Amplifier	A53304B008		
Assembly Drawings			
L102 Module Assembly	D53304A003	Rev	C*
Phase Lock Unit for 2 kHz Reference	C53304A013		
Phase Lock Board for 2 kHz Reference	B53304A002	Rev	F
130 Hz Amplifier and Comparator Board	B53004A004	Rev	Α
X5 Multiplier Board	A53304A005		
Monitor Detector Amplifier Board	A53304A006		
2-Stage 500 MHz Amplifier	A53304A008	Rev	Α
Printed Circuit Boards			
Phase Lock Board for 2 kHz Reference	B53304Q002	Rev	F
X5 Multiplier Board	B53304Q004	Rev	Α
Monitor Detector Amplifier Board	B53304Q005	Rev	В
Board for 130 Hz Amplifier and Comparator	B53304Q006	Rev	Α
Mechanical Drawings			
Center Mounting Plate	D53304M003	Rev	D
Module Front Panel	B53304M001	Rev	Ā
Box for Phase Lock Unit, 2 kHz Reference	B53304M006	Rev	A
Component Mounting Spacers	B53304M008		
Box for 130 Hz Amplifier and Comparator	B53304M009		
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* Requires updating as of 12/10/91.

(7) Design of the LO Receiver Module.

A block diagram of the LO Receiver is shown in the lower half of Fig. 2. An input reference signal at 500.000 MHz from the LO Transmitter is applied at J10. This signal is split in a three-way power divider. The first output goes to a monitoring detector, the output of which is amplified to -1 volt in an amplifier for which the circuit is shown in Fig. 3.

The second output of the power divider is used to lock a VCXO at 500.000 MHz, using a phase-lock unit of the type described below in section 8. The VCXO output is filtered to remove harmonics of the frequency of the crystal (62.5 MHz) and harmonics of 500 MHz. The signal used to lock the VCXO comes from a 10 dB coupler and goes to the VCXO port of the phase lock unit.

The third output of the 500 MHz power splitter goes to the modulated reflector that produces sidebands at \pm 1.953 kHz, which are returned for the round-trip phase measurement. The circuit of the modulated reflector is shown in Fig. 8.

The 100 MHz reference signal from the LO Transmitter enters at J8, and is split two ways. One component is amplified and provides the output at J1. The other goes to a monitoring detector, the output of which is amplified to -1 volt.

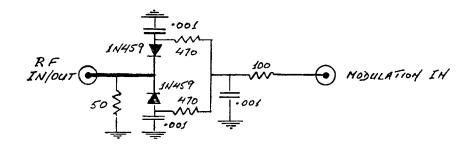


Fig. 8 Circuit of the modulated reflector.

(8) The LO-Receiver Phase Lock Unit.

A circuit diagram of the phase lock unit is given in Fig. 9. It is designed to operate with both VCXO and reference frequencies of 500 MHz as inputs. Input levels for these two signals are both -4 ± 2 dBm. With 14.5 dB typical gain in the Al8-1, and allowing 3.5 db attenuation in the DS-327 power divider and the JH-140 hybrid, the input levels to the PD-120 phase detectors are 7 ± 2 dBm. Of the two phase detectors in Fig. 9, the one on the right controls the phase lock loop and the one on the left the lock detector.

The output of the loop PD-120 drives the integrating amplifier LH0022 (U5), which drives a LF411 (U1) inverting amplifier with voltage gain of -0.46. The output of the LF411 stage controls the frequency of the VCXO. Note that at the VCXO a diode is connected from the frequency control terminal to ground to protect the VCXO from any negative voltage that might accidentally occur at that point. (In the LO Transmitter a similar protective diode is located in the phase lock unit.) If the loop is not locked, the lock indicator circuitry causes pin 4 of the AD7510D1 (U6) to be at TTL high, so the switch at pins 13-14 is closed. (The AD7510D1 switches are closed with TTL high on the control inputs.) Thus the summing junction of the LH0022 is connected through 2 M to -15 volts, which causes the output to sweep positive. When it goes higher than the 13.2 volts on pin 2 of the LM393 (U1), pin 1 goes high and the switch at pins 11-12 of AD7510D1 shorts the integrating capacitor C1. The output of the LH0022 then falls to zero and starts to sweep up again in voltage until lock is obtained. The sweep action is similar to that described for the LO transmitter phase lock unit. At the output of the LF411 that controls the VCXO frequency (U1), the sweep is negative going, from 6 to 0 (± 0.5) volts. The printed circuitry associated with Ul has been designed so that if the existing components are removed it can be reconnected as a non inverting amplifier, which may be convenient if the unit is ever used with a different VCXO.

When the loop is in lock the output of the lock-detector PD-120 is approximately -0.3 volts, and this is amplified by a factor of -10 in U3 and applied to pin 6 of the LM393 (U2) comparator. The voltage on pin 5 of the LM393 is set to 2.8 volts, and thus the output on pin 7 is at TTL low for lock and high for no lock. When the loop is locked this voltage from pin 7 opens the contacts at pins 9-10 of the AD7510D1 (U6), and thereby lights a front panel LED. Note that if the loop is not locked but the VCXO is producing a low frequency beat waveform at the output of the lock detector PD-120, the LED may glow faintly, being lit on the negative half cycles of the beat waveform. This effect is reduced by the 0.002 μf capacitor in parallel with the 47k feedback resistor of U3, which reduces the frequency response. Note that this capacitor must not be too large or it will slow down the lock detector action. The lock detector must open the switch at pins 13-14 of the AD7510D1 quickly enough to stop the sweep action when lock is found or lock will not be retained.

If a frequency of 500 MHz is applied to one input terminal of a PD-120 phase detector, and a frequency a few kHz different is applied to the other, both at a level of 7 dBm, the output shows the beat frequency as a triangular waveform of amplitude 0.7 volts p-p. This becomes a sinusoid only if the

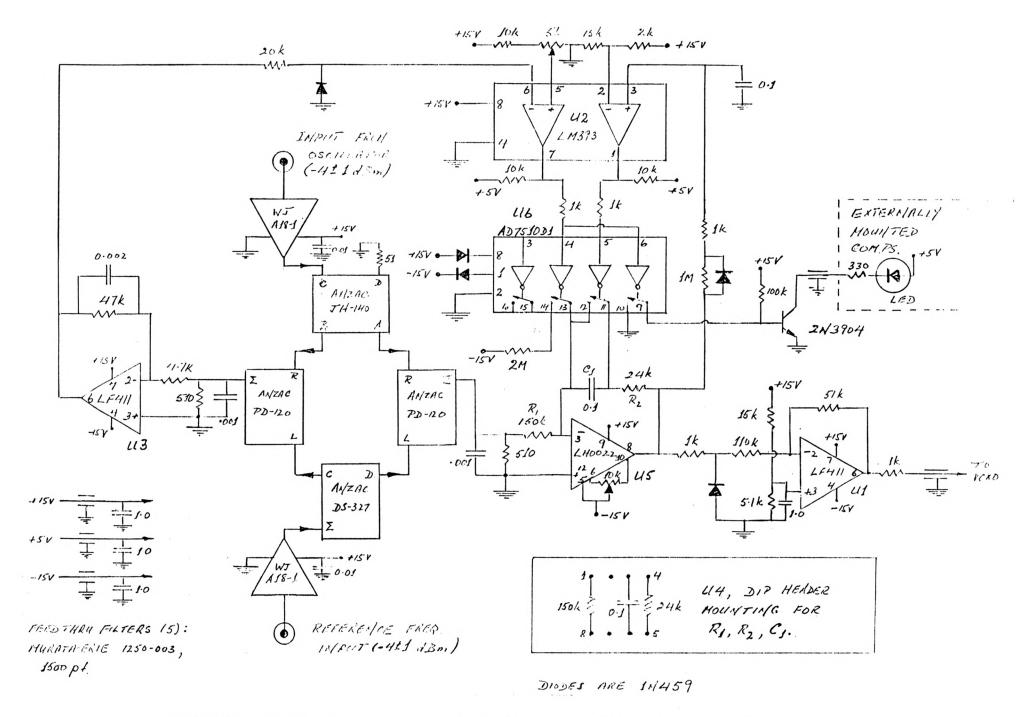


Fig. 9 Circuit diagram of the phase lock unit used in the LO Receiver module. This unit is designed for use with input signals at 500 MHz.

1/1/92

inputs are reduced to 0 dBm. The recommended level on the PD-120 data sheet is 7 dBm, and the phase sensitivity is then 0.22 volts/radian. (Note this is a measured value which was consistent for several individual units. The value indicated by the curve in the PD-120 data sheet is 8.5 mv/deg. or 0.48 volts/radian, which appears to be wrong). Then for a tuning constant of 8 kHz/volt for the VCXO, values of R1=150k, R2=24k and C1=0.1 μ f, and the LF411 stage gain of 0.46, the natural frequency of the loop is 93 Hz and the damping factor is 0.70. The components R1, R2, and C1 are mounted on an eight-pin D1P header (U4) on the board for convenience in adjustment.

(9) Inputs and Outputs of the LO Receiver.

OSP Connectors, Rear Panel

- Jl 100 MHz output
- J2 500 MHz output
- J8 100 MHz input
- J9 1.953 kHz input
- J10 500 MHz input

42-Pin AMP Connector, Rear Panel

- 1 Monitor detector level for 100 MHz
- 2 Monitor detector level for 500.002 MHz
- 10 +5 volts input
- 16 +15 volts input
- 17 -15 volts input
- 27 Lock indicator, TTL low for loop in lock
- 34 Ground
- 42 Ground

Front Panel

- BNC Loop voltage at oscillator frequency-control terminal
- LED Lock indicator, on for loop in lock

(10) Checkout of the LO Receiver.

Refer to the block diagram in the lower half of Fig. 2. The nominal input level for the 500 MHz signal is -1 dBm, which allows for 12 dB of loss in the cable and in attenuators that may be inserted for level adjustment.

- (1) Apply -1 dBm at 500 MHz to OSP connector J10 and check the output level of the monitoring detector at output 1 of the three-way power splitter. Set the output of the detector amplifier to -1 volt.
 - (2) Check and adjust the phase-lock unit (Fig. 9) as follows.
 - (a) Remove IC's except for Al8-1 amplifiers. Insert signals at approximately 500 MHz but differing in frequency by a few kHz into the two inputs. The signal levels should be -4 \pm 2 dBm. One of the inputs will be from the VCXO, and for this test it is convenient to disconnect the frequency control signal to the VCXO and ground the terminal at the

- oscillator. The other input can be from a signal generator applied to OSP connector J10. At the outputs of the two PD-120 phase detectors the beat waveform should have an approximately triangular sawtooth profile. Amplitudes should be between 0.65 and 0.80 volts p-p. DC offsets should be no more than a few mv. The waveforms from the two phase detectors should be in phase quadrature.
- (b) Insert the LH0022 (U5). Remove RF inputs to the unit and ground the output of the loop phase detector. This grounding can be done by connecting pins 7 and 8 on the DIP header (U4). Monitor pin 8 of the LH0022 and adjust the 10k trimpot for this IC so that a voltage of a few volts remains steady as described for the transmitter phase lock unit. Remove the phase detector grounding.
- (c) Insert the other IC's. Set the 5k trimpot so that the potential on pin 5 of the LM393 (U2) is 2.8 volts. Set up a condition in which the loop cannot lock: e.g. remove reference input or remove the frequency control to the VCXO and ground the terminal on the VCXO. The control output from the loop to the VCXO should sweep with a period of about 200 ms from 6 \pm 0.5 volts to zero or -0.5 volts. With all connections restored the loop should now lock.
- (d) Vary the reference frequency and the VCXO should be able to lock over a range of about 20 kHz. The range may not be centered on 500 MHz, and the center frequency will depend on the individual VCXO. Monitor the frequency control voltage of the VCXO on an oscilloscope and see that it varies as the VCXO follows the reference frequency.
- (3) The 500 MHz output power level at J2 should be 15 \pm 1 dBm. Adjust the attenuator at the VCXO output if necessary. Also check the signal with a spectrum analyzer. All harmonics and subharmonics should be at least 60 dB below the wanted output.
- (4) Insert a dual directional coupler into the 500 MHz input line at J10. Apply a $1.9 \, \text{kHz}$, TTL-level signal to OSP connector J9. The level of the sidebands at $\pm 1.9 \, \text{kHz}$ on the signal going back from the LO Rx module should be -30 to -35 dB with respect to the forward going signal at 500 MHz to the module. It may be convenient to increase the frequency of the modulation from $1.9 \, \text{kHz}$ to, say, 10 kHz to help isolate the sidebands if the resolution of the spectrum analyzer is insufficient. The level of the sidebands does not vary significantly with frequency over such a range.
- (5) Apply a signal at 100 MHz and 6 dBm to OSP connector J8. The output power at J1 should be 16 ± 1 dBm. If necessary, adjust the attenuator in this signal path at the output of the two way power splitter.
- (6) With the same input level at 100 MHz, set the output of the amplifier for the level monitoring detector to read -1 volt.

(11) List of Drawings, Artwork, and Bills of Materials for LO Receiver,

Schematic and Logic Diagrams Phase Lock Circuit for 500 MHz Reference Monitor Detector Amplifiers Modulated Reflector	B53304S001 Rev D A53304S006 Rev A A53304S007
Bills of Materials	
L105 Module	A53304B009*
Monitor Detector Amplifier Board	A53304B006
Modulated Reflector	A53304B007
Assembly Drawings	
L105 Module Assembly	D53304A009 Rev A*
Phase Lock Board for 500 MHz Reference	C53304A001 Rev D
Monitor Detector Amplifier Board	A53304A006
Modulated Reflector Board	A53304A007
Printed Circuit Boards	
Phase Lock Board for 500 MHz Reference	D53304Q001 Rev C (2 parts)
Drill Dwg for above	C53304P001 Rev D
Modulated Reflector Board	B53304Q003 Rev A
Monitor Detector Amplifier Board	B53304Q005 Rev B
Mechanical Drawings	
Center Mounting Plate	D53304M004 Rev F
Module Front Panel	B53304M002
Box for Phase Lock Unit, 500 MHz Reference	C54120M011-4
Rework for above box	B53304M005 Rev C
Top Cover for above box	C54120M009-4
Bottom Cover for above box	B53304M015
Component Mounting Spacers	B53304M010 Rev A (2 parts)

^{*} Requires updating as of 12/10/91.

(12) Specifications and Information Sheets.

VCXO Vectron CO-283VW-OR

Diode Quad Alpha DMF6288

Active Filters Data Delay Devices 5151-200 and 5151-2500

Mixer Mini-Circuits ZFM-150

Phase Detector Anzac PD-120

Power Divider Anzac DS-327

Quadrature Hybrid Anzac JH-140

Integrated Circuits (Note that only the first page of catalog information is

given for the following items.)

AD7510D1

AD7512D1

LF411

LH0022

LM393A

MC4044

UTO-572

UTM-1055

WJ-A18-1

WJ-A19



Vectron Laboratories, Inc.

166 Glover Avenue, Norwalk, Connecticut 06850 Telephone: 203/853-4433 TWX: 710/468-3796

May 20, 1987

National Radio Astronomy 2015 Ivy Rd. Charlottesville, VA 22903

Attention: Karen Thach

Subject: Your Purchase Order No. B01980

Dear Ms. Thach:

On the subject purchase order you ordered our CO-283VW-R at 500 MHz crystal oscillator. Our part numbering system has recently been revised and the correct part number for this oscillator is CO-283VW-OR at 500 MHz. The enclosed data sheet shows this.

We'd appreciate your confirming order reflecting the "CO-283VW-OR" part and regret any inconvenience this causes you.

Cordially,

Bill Zarkower Regional Manager

BZ/11s Enclosure cc: TVA

VCXOs for Phase Locking









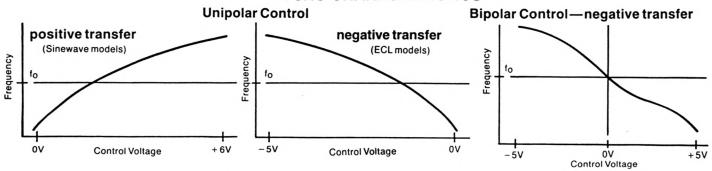


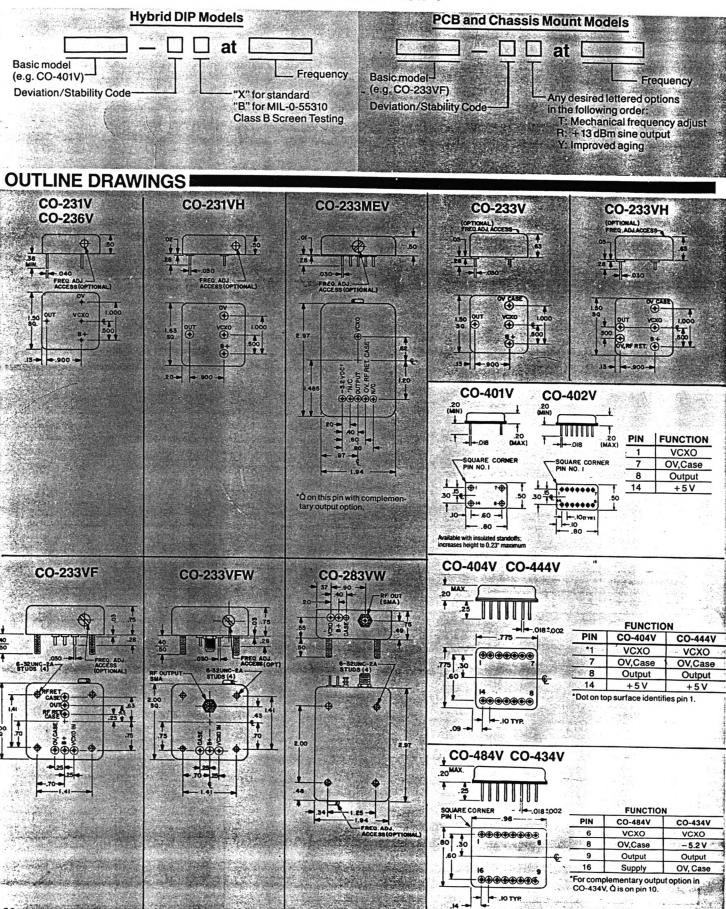




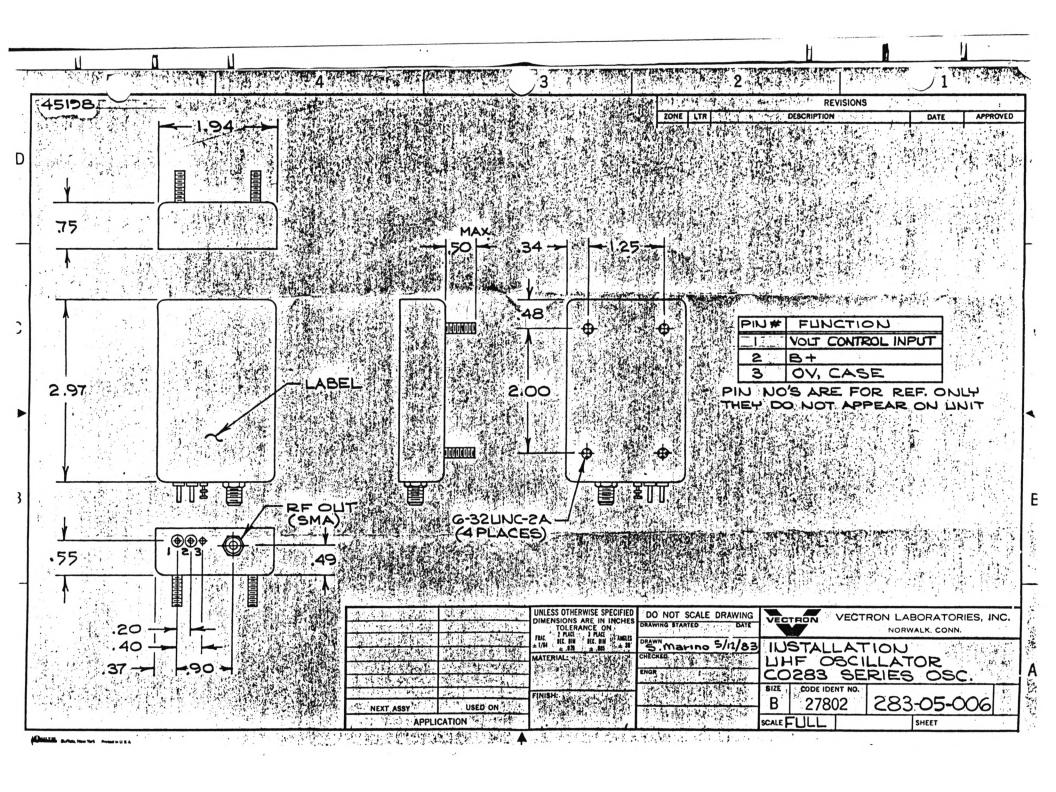
		ECL	SINEWAVE						
Configuration	PC board mount	low profile hybrid DIP	PC boa	urd mount			nount with connector	low profile hybrid DIP	A. C. C.
Series	CO-233MEV	CO-434V	(a) CO-233V (b) CO-233VH	CO-233VF		. CO-233VFW	CO-283VW-OR	CO-484V	
Center Frequency	8-200 MHz	8-200 MHz	(a) 8-149.9 MHz (b) 150-200 MHz	8-400 MHz	z	8-400 MHz	400 1-600 MHz	8-200 MHz	
Output Level	10K outp	compatible out to 110 MHz out above 110 MHz ary output optional)	Harmonics are - 2	20 dBc. Internal m Harmonic and su	ultipli bharn		e in CO-484V). love 70 MHz, and resultuced to -30 dBc or $-$		
Supply	- 5.2 Vo	Ic at 30-60 mA	+ 15 Vdc (+ 12 Vd	lc to + 24 Vdc opt	ional)	; current ranges from	15 mA at 8 MHz to 100	mA at 600 MHz	_
Deviation/Stability Alternatives Çontrol Voltage	Code 0 A B C D E F G H I' J K L' M N	Range 0/+50°C 0/+50°C 0/+50°C 0/+50°C 0/+50°C 0/+70°C 0/+70°C 0/+70°C -20/+70°C -20/+70°C -20/+70°C -40/+85°C -40/+85°C -55/+85°C -55/+85°C rest frequency at 0V) V to ±10V or CO-233MEV	Temperature Stability ± 10 ppm ± 20 ppm ± 35 ppm ± 35 ppm ± 40 ppm ± 50 ppm ± 50 ppm ± 50 ppm	* ± 3V	} (trans / to ±	(±200 ppm de • They are onl • Linearity of	y available at frequenci ± 10% is standard ECL models above 110 straint). odels above 110 MHz straint). equency at OV) or CO-283VW	es up to 25 MHz	
Linearity			± 20% smooth mono	tonic characterist	ic (±	equired for ECL models 10% linearity available nd with deviation/state s up to 25 MHz)		
Modulation Rate		•		; higher modulation					
Modulation Input Z		Greater than 50kΩ							
Aging Rate			ls: 5 ppm for first ye		ar the	reafter.	0 ppm total over 10 yea	ars.	_
Mechanical Tuning Option	"Ţ"	N/A "T" ind	"T" icates that a mechanic	"T", cal tuning option is	s avail	T" able; add "T" to mode	l number	N/A	
Size (See page 66)	2" x 3" x ½"	0.8" x 0.98" x 0.2" 16 pin double DIP	1½" x 1½" x ¾ CO-233V & VH differ in pin configuration	2"×2"×¾	ľ	2"x2"x¾"	2"x3"x¾"	0.8" x 0.98" x 0 16 pin double DIP	.2"

VCXO CHARACTERISTICS





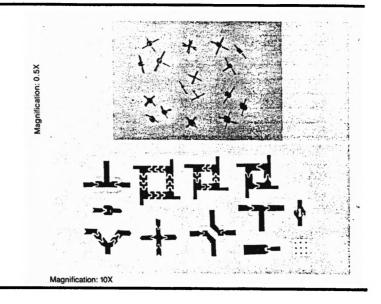
Markings do not appear on units—for reference only; case dimension tolerances are ± .02".



Silicon Beam-Lead and Chip Schottky Barrier Mixer Diodes

Features

- Ideal for MIC
- Low 1/f Noise
- Low Intermodulation Distortion
- Low Turn On
- Hermetically Sealed Packages



Description

Alpha beam-lead and chip Schottky barrier mixer diodes are designed for applications through 40 GHz in Ka-band. The beam-lead design eliminates the problem of bonding to the very small junction area that is characteristic of the low capacitance involved in microwave devices.

Beam-lead Schottky barrier mixer diodes are made by deposition of a suitable barrier metal on an epitaxial silicon substrate to form the junction. The process and choice of materials result in low series resistance along with a narrow spread of capacitance values for close impedance control.

A variety of forward knees is available, ranging from a low value for low, or starved, local oscillator drive levels to a higher value for high drive, low intermod mixer applications.

The beam-lead diodes are available in a wide range of packages as shown. They may also be mounted on the customer's circuit or on other substrate configurations. For those customers who prefer chip and wire for their MIC work, Alpha can supply a complete line of bondable chips. Capacitance ranges and series resistances are comparable with the packaged devices that are available through Ka-band. The unmounted diodes are especially well suited for use in microwave integrated circuits. The mounted devices can be easily inserted as hybrid elements in stripline, microstrip and other such circuitry.

Applications

Beam-lead and chip Schottky barrier diodes are categorized by noise figure for mixer applications in four frequency ranges: S, X, Ku and Ka-bands. However, they can also be used as modulators, high speed switches and low power limiters.

RF parameters, capacitance and breakdown voltage on chips and beam-lead diodes are tested on a sample basis, while production testing consists of series resistance and forward voltage measurements. A separate data sheet in this section describes beam-lead and chip diodes that are optimized for detector applications.

Several types of semiconductor-barrier metal systems are available, thus allowing proper selection for optimum mixer design. For most applications the N-type silicon, low drive types are preferable, especially for starved L.O. mixers. For doppler mixers, motion detectors or applications requiring low audio (1/f) noise, the P-type silicon, low drive types are preferred. For high level mixer applications requiring low intermodulation products, the N-type silicon, high drive types are most desirable.

Beam-lead diodes are ideally suited for balanced mixers, since they exhibit low parasitics and are extremely uniform. A typical $V_{\rm f}$ vs $I_{\rm f}$ curve is shown in Figure 1.

Typical noise figure vs L.O. drive is shown in Figure 2 for single N-type, low drive diode types.

Typical mixer circuits are shown in Figure 3 in order of complexity. The circuits shown in Figures 3a and 3b are recommended for narrower band applications.

The matching network can be an "L" network using discrete components at lower frequencies or a section of transmission line. The double balanced mixer in Figure 3c is recommended for broadband operation where noise figure is less important. The use of high drive diodes in this circuit allows the use of increased L.O. drive with a resultant decrease in intermodulation distortion.

See Sections 2 and 7 for Application Notes:

80800	Mixer and Detector Diodes
80850	Handling Precautions for Schottky Barrier and Point Contact Mixer and Detector Diodes
80000	Bonding Methods: Diode Chips, Beam-Lead Diodes and Capacitors

Silicon Beam-Lead and Chip Schottky Barrier Mixer Diodes

FREQUENCY TABLE

Band	Frequencies (GHz)		
S	2 to 4		
С	4 to 8		
X	8.2 to 12.4		
Ku	12.4 to 18.0		
К	18.0 to 26.5		
Ka	26.5 to 40.0		

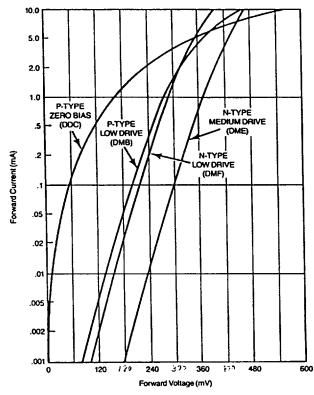


Figure 1a. Typical Forward DC Characteristic Curves — Voltage vs Current

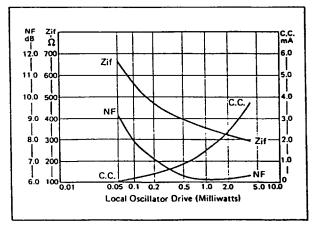


Figure 2. Typical X-Band Low Drive Mixer Diode

— RF Parameters vs Local Oscillator
Drive

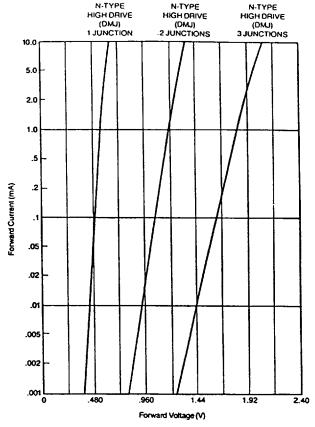


Figure 1b. Typical Forward DC Characteristic Curves — Voltage vs Current

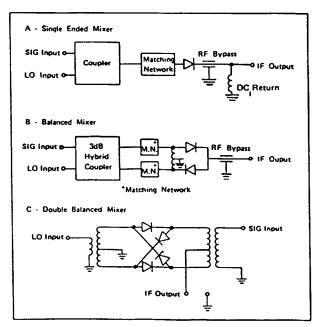


Figure 3. Typical Mixer Circuits

Silicon Beam-Lead and Chip Schottky Barrier Mixer Diodes

Beam-Lead Quad Rings, N-Type, High Drive, 12 Junction

Frequency	Туре		NF ⁽¹⁾ dB	B PF		Rs ⁽²⁾ Ω		rnA NV	△V _F ⁽⁴⁾ 1mA mV
Band	Number	Outline	Max.	Min.	Max.	Max.	Min.	Max.	Max.
- 0	DMJ4766	132-022		0.05	0.15	21	1650	2250	25
e 0	DMJ6564	398-022	_	0.05	0.15	21	1650	2250	25

Beam-Lead Quad Bridges, N-Type, Low Drive

Frequency	Type		NF ⁽¹⁾ dB		V F	Rs ⁽²⁾ Ω	l 1r	/ _f nA ıV	△V _F ⁽⁴⁾ 1mA	V _в 10µА
Band	Number	Outline	Max.	Min.	Max.	Max.	Min.	Max.	mV Max.	V Min.
	DMF3059	132-004		_	1.20	9	225	350	15	1.0
L	DMF4540	337-004			1.20	9	225	350	15	1.0
3	DMF5848A	132-004	6.0	0.30	0.50	3	225	300	15	2.0
3	DMF5848	132-004	6.5	0.30	0.50	7	225	300	15	2.0
3	DMF3076A	294-004	6.0	0.30	0.50	3	225	300	15	2.0
S	DMF3076	294-004	6.5	0.30	0.50	7	225	300	15	2.0
S	DMF3067A	295-004	6.0	0.30	0.50	3	225	300	15	2.0
S	DMF3067	295-004	6.5	0.30	0.50	7	225	300	15	2.0
S	DMF3063A	325-004	6.0	0.30	0.50	3	225	300	15	2.0
S	DMF3063	325-004	6.5	0.30	0.50	7	225	300	15	2.0
X	DMF6288A	132-004	6.5	0.15	0.30	7	250	325	15	2.0
X	DMF6288	132-004	7.0	0.15	0.30	12	250	325	15	2.0
λ	DMF3077A	294-004	6.5	0.15	0.30	7	250	325	15	2.0
X	DMF3077	294-004	7.0	0.15	0.30	12	250	325	15	2.0
X	DMF6558A	295-004	6.5	0.15	0.30	7	250	325	15	2.0
X	DMF6558	295-004	7.0	0.15	0.30	12	250	325	15	2.0
Х	DMF4352A	325-004	6.5	0.15	0.30	7	250	325	15	2.0
Х	DMF4352	325-004	7.0	0.15	0.30	12	250	325	15	2.0
Х	DMF3079A	364-004	6.5	0.15	0.30	7	250	325	15	2.0
Х	DMF3079	364-004	7.0	0.15	0.30	12	250	325	15	2.0
Ku	DMF6298A	132-004	7.5	0.05	0.15	16	275	350	15	2.0
Ku	DMF6298	132-004	8.0	0.05	0.15	25	275	350	15	2.0
Ku	DMF3078A	294-004	7.5	0.05	0.15	16	275	350	15	2.0
Ku	DMF3078	294-004	8.0	0.05	0.15	25	275	350	15	2.0
Ku	DMF6574A	295-004	7.5	0.05	0.15	16	275	350	15	2.0
Ku	DMF6574	295-004	8.0	0.05	0.15	25	275	350	15	2.0
Ku	DMF3080A	364-004	7.5	0.05	0.15	16	275	350	15	2.0
Ku	DMF3080	364-004	8.0	0.05	0.15	25	275	350	15	2.0

Notes:

¹ $N_e = 1.5 \text{ dB}$, L.O. = 1.0 mW, $R_e = 100 \Omega$

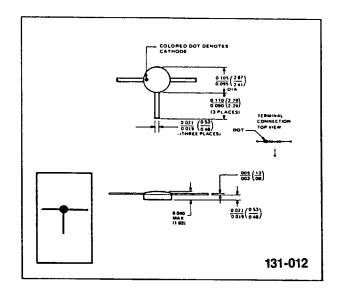
1.3 GB, L.O.	= 1.0 11144, D(= 10073	
Band	Test	Frequency (GHz)
S		3.1
X		9.4
Ku	***************************************	16.0
Ka	***************************************	34.9

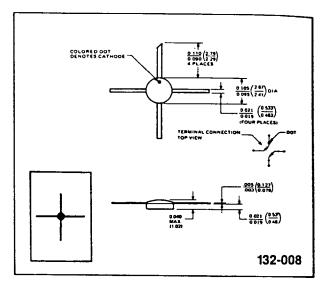
R₁ = R₁ - R₈ where R₁ is the total resistance measured across the diode terminals and R₈ is the barrier resistance (2.8Ω for a Schottky barrier diode measured at 10mA. For multiple junction devices, the R₈ would be 2.8Ω times the number of junctions between the diode terminals).

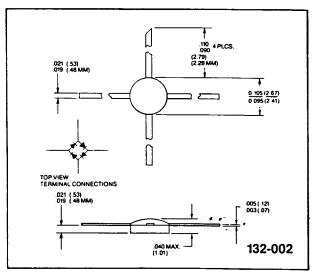
Electrical characteristics are specified for each junction except for those devices containing two or more junctions in series per arm. For these cases, the specification is for the arm.

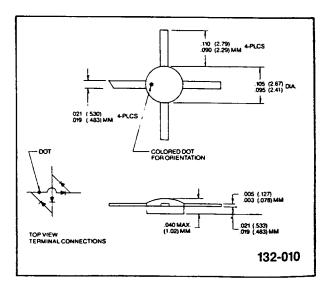
^{4.} Difference in forward voltage between leads within a pair or quad.

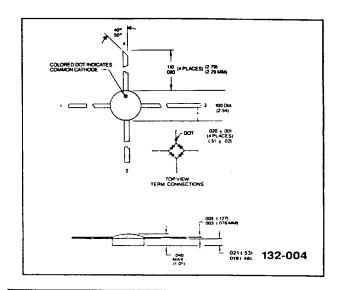
Outline Drawings

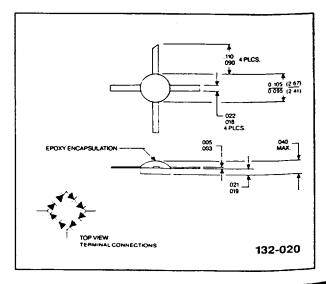












J, inc.

385 Lakeview Ave., Clifton, N.J. 07011 785 Lakeview Tel: (201) 772-1106 THE PERSON DE LA COMPANIE DE LA COMP



P/N 5151

SHORT FORM -CATALOG

DIP-ACTIVE FILTERS SERIES 5151-5353

PART NO.

5151-400

5151-1,000 5151-1,200

5151-2,500

5151-4.000

5151-20,000

SPECIFICATIONS

PART NO.

5151-1

5151-10

5151-40

5151-50

5151-200

- · Transfer characteristics Buth
- Gein in pess-band 0 db ± .2 db.
- · Cut-off frequency accuracy ± 2% @ -3 db. m input voltage — 10 volts peak.

3 db FREQUENCY

(HZ)

10

20 40 50

LOW-PASS FILTERS

- Skirt Attenuation 24 db / octave
- · DC drfft 20uV / °C typical.
- Supply Voltage ± 15V typical (±9V to ±18V operational).
- Temperature range 0° to + 70°C (standard); -55°C to + 125°C (on requ Temperature Coefficient .03% / °C. Better on request.

3 db FREQUENCY (HZ)

100

160

400

500

1,000

HIGH-PASS FILTERS

PART NO.

5353-2,500

5353-3,250

5353-4.000

5353-13,000

5353-16,000

5353-20,000

- er Consumption 200MW Maximum.

PART NO.

5353-100

5353-160

5353-400

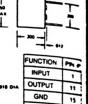
5353-500

5353-1,000

5353-1,800



[



12

NOTE: The above table gives only a small number of designs available. Many other designs are availabe on request. Any frequency from 1HZ to 25 KHZ can be selected. To make a part number, simply use the basic series number and the cut-off frequency.

3 db FREQUENCY (HZ)

1,000

2,500

- 4,000 5,000

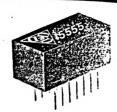
20,000

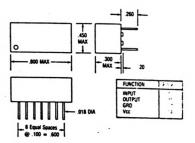
BAND-PASS FILTER SERIES 5555

PART NO.	fc(Hz)	PART NO.	fc(Hz)	PART NO.	fc(Hz)
5555-360	360	5555-1260	1260	5555-2280	2280
5555-420	420	5555-1320	1320	5555-2340	2340
5555-480	480	5555-1336	1336	5555-2400	2400
5555-540	540	5555-1380	1380	5555-2460	2460
5555-600	600	5555-1440	1440	5555-2520	2520
5555-560	660	5555-1477	1477	5555-2580	2580
5555-697	697	5555-1500	1500	5555-2640	2640
5555-720	720	5555-1560	1560	5555-2700	2700
5555-770	770	5555-1620	1620	5555-2760	2760
5555-780	780	5555-1633	1633	5555-2820	2820
5555-840	840	5555-1680	1680	5555-2280	2880
5555-852	852	5555-1740	1740	5555-2940	2940
5555-900	900	5555-1800	1800	5555-3000	3000
5555-941	941	5555-1860	1860	5555-3060	3060
5555-960	960	5555-1920	1920	5555-3120	3120
5555-1020 5555-1080 5555-1140 5555-1200 5555-1209	1020 1080 1140 1200 1209	5555-1980 5555-2040 5555-2100 5555-2160 5555-2220	1980 2040 2100 2160 2220	5555-3180 5555-3240 5555-3300 5555-3360	3180 3240 3300 3360

SPECIFICATIONS

- · G. 1 @ fc: 10 db typical.
- · Center Frequency Accuracy: ±1%.
- · Input Voltage: 1v rms Max.
- Supply Voltage: 15Vdc.
- Temperature Range: 0° to 70°C. Temperature Coefficient: .03%/°C.
- Power Consumption: 625 MW @ 25°C.
- · Output Load: 600 Min.





LOW PROFILE FILTERS SERIES 1100

CASE Metal flat case to reduce hum pick-up. PINS Straight pins for PC mounting

LOW-PASS

PART	Imp.	PASS-E	BAND	. STOP-BAND	CASE
NO.	IN/OUT	(1db)	(3db)		NO.
1101-1	10K	DC to 460Hz	600Hz	40db above 750Hz	1
1101-2	600	DC to 3KHz	3.4KHz	40db above 4.2KHz	l i
1101-3	10K	DCto 4.4KHz	5KHz	43db above 6.3 KHz	1
1101-4	1K	DC to 9KHz	10KHz	43db above 12.8KHz	11'
1101-5	600	DC to 15KHz	18KHz	43 db above 23KHz	1
1101-6	600	DC to 43KHz	50KHz	43db above 64KHz	2

HIGH-PASS

PART	Imp.	PASS-BAI	ND	STOP-BAND	CASE	
NO.	IN/OUT	(1db)	(3db)		NO.	
1102-1	10K	300Hz & above	200Hz	40db below 140Hz	1	
1102-2	10K	600Hz & above	400Hz	40db below 280Hz	1	
1102-3				40db below 560Hz	1	
1102-4	.10K	3KHz & above	2KHz	40db below 1.4KHz	2	
1102-5	10K	6KHz & above	4KHz	40db below 2.8KHz	2	





BROAD BAND-PASS

PART	Imp.		STOP-BA	CASE	
NO.	IN/OUT	PASS-BAND	BELOW	ABOVE	NO.
1103-1		1KHz to 2KHz	0.5KHz	4KHz	3
1103-2		2KHz to 4KHz	1KHz	8KHz	3
1103-3	10K	4KHz to 8KHz	2KHz	16KHz	3
1103-4	10K	10KHz to 20KHz		40KHz	4

CASE DIMENSIONS

CASE	Α		В		D .		F		Н	
NO.	IN.	M.M.	IN.	M.M.	IN.	M.M.	IN.	M.M.	IN	1.1.81
_ 1	1.4	35.56	1.875	47.63	1.4	35.56	2.0	50.8	0.5	
2	1.4	35.56	2.0	50.8	0.8	20.32	1.5	38.1	0.375	G :
3	1.4	35.56	2.0	50.8	0.8	20.32	1.5	38.1	0.5	12 "
4	0.8	20.32	1.25	31.75	1.0	25.4	1.75	44.45	0.375	94.

DATA DELAY DEVICES INC. • 385 Lakeview Avenue, Clifton, N.J. 07011 • (201) 772-1106

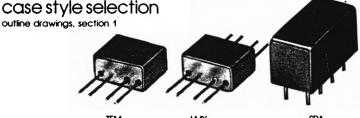
broadband, high dynamic range

Frequency Mixers

LEVEL 10 (+10dBm LQ, up to +5dBm RF)

50 KHz to 3 GHz performance data curves, tables, Model Index section 2

outline drawings, section 1





		FREQU MI		CON	VERS		LOSS	1	LO-RI	F ISO	LATIC	ON, d	В	ı	O-IF	ISO	ATIO	N, di	3	PRIC	E, \$
	MODEL	LO/RF	IF	Mid-I	Band n		tal nge		L		4	ι		1		,	и		U		
	NO.	f _L -f _U		Тур.			Max.	Typ.	Min.	Typ.		Тур.		Typ.	Min.	Тур.		Тур		Ea.	Qty.
TFM	TFM-15	10-3000	10-800	6.3	8.0	6.5	8.5	35	25	35	25	35	25	30	20	30	20	30	20	49.95	(1-9)
case B13	TFM-150*	10-2000	DC-1000	6.0	8.0	6.5	8.0	32	25	35	25	35	25	33	20	30	20	30	20	39.95	(1-9)
LMX	LMX-123	10-3000	10-3000	7.5	8.0	7.5	8.5	35	25	35	20	30	15	35	25	30	25	30	20	59.95	(6-24)
case 8848	LMX-148	10-1500	DC-1500	6.0	7.0	6.0	10	45	40	35	30	25	20	40	35	35	25	20	12	24.95	(6-24)
SRA	SRA-215	.05-1500	.05-500	6.0	7.5	7.0	9.0	25	20	35	25	30	20	25	20	35	25	25	15	23.95	(5-24)
case A01	SRA-220	.05-2000	.05-500	6.0	7.5	7.0	9.0	25	20	40	30	30	20	25	20	40	30	25	15	26.95	(5-24)
ZFM	ZFM-15	10-3000	10-800	6.3	7.5	6.5	8.5	35	25	35	25	35	25	30	20	30	20	30	20	79.95	(1-9)
case K18	ZFM-150	10-2000	DC-1000	6.0	7.0	6.5	8.0	32	25	35	25	35	20	33	28	30	20	25	20	59.95	(1-9)

L=low range ((to 10 f())

 $M = mid range (10f_L to f_U/2)$ $m = mid band (2f_1 to f_1/2)$

 $U = upper range (f_U/2 to f_U)$

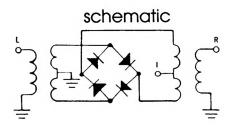
harmonic attenuation

		•			~~					• •			
		RF CAL		М	ODE	LIF	M-1	•					
ē	1	0	0	31	17	42	32	48	47	52	65	59	
Order	2	83	38	45	39.	4 8	46	76	69	70,	64	71	
盎	3	87	39	49	37	52	42	57	63	65	65	65	
S	4	89	64	60	58	56	59	60	62	69	74	70	
Harmonics	5	90	74	69	59	72	55	74	58	71	67	72	
호	6	83	83	76	74	67	69	67	72	70	74	78	
	7	83	76	83	81	79	69	71	66	70	69	77	
	8	84	75	76	81	82	77	77	80	78	78	77	
	9	84	77	76	75	82	80	81	82	80	79	80	
	10	81	76	76	74	75	80	81	81	81	80	81	
			1	2	3	4	5	6	7	8	9	10	
				Harr	noni	c LC	Or	der					

Model: TFM LO = +10 dBm, 969.01 MHzRF = 0 dBm, 999.1 MHz

NOTES:

- NON-HERMETIC
- Below 10 MHz IF, conversion loss increases up to 6dB higher as frequency decreases to DC.
- 1. For quality control procedures, environmental specifications, and Hi-Rel, MIL and TX description see section 1.
- 2. Absolute Maximum Ratings, RF power 50 mW level 10, 200 mW level 13, peak IF current 40 mA, see section 1.
- 3. For connector types and case mounting options, see case style outline drawings, section 1.
- 4. Prices and specifications subject to change without notice.



PHASE DETECTOR 5-1000 MHz

Wide Bandwidth Low DC Offset

Guaranteed Specifications*

(From -55°C to +85°C)

Frequency Range		5-1000 MHz
Maximum DC Output	5-500 MHz 5-1000 MHz	300 mV Min 250 mV Min
Isolation (L-R)	5-200 MHz 200-500 MHz 500-1000 MHz	50 dB Min 40 dB Min 30 dB Min
DC Offset (100 MHz RF)		1.0 mV Max

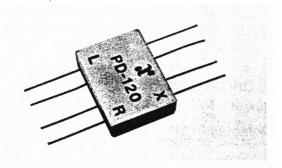
Operating Characteristics

Impedance	
(L,R Ports)	50 Ohms Nominal
Load (X Port)	500 Ohms
Input Power (L&RPor	ts) + 7 dBm Nominal
Maximum Input (Non-	Destruct)
Total Power	300 mW Max @ 25°C
	Derated to 85 °C @ 3.2 mW/°C
DC Output Polarity	Negative
Package Type	Flatpack (FP-2)
	(See page 474 for physical dimensions.)

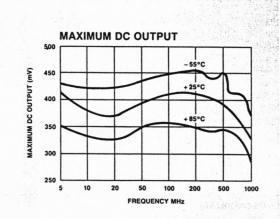
Environmental

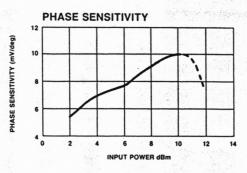
These units are designed to meet the environmental and screening requirements of Table 1A, page 496 of the Adams-Russell catalog.

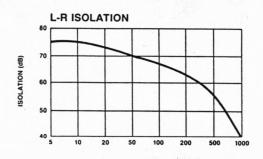
Pin Configuration RF; P8, LO; P5, IF; P4.
All other pins and case are ground.



Typical Performance







Ordering Information

Model No.	Part No.	Connectors	Unit Price (5-9 Units)
PD-120	8519	Pin	\$62
D-1 1			

ANZAC

Adams Russell

80 Cambridge Street, Burlington, MA 01803 Fax (617) 273-1921

^{*}All specifications apply when operated at +7 dBm available LO and RF power and 50 ohms impedance at the L & R ports and with 500 ohm load at the X port.

Broadband, IN Phase Divider Low Loss — 0.3 dB Typical Amplitude Balance — 0.05 dB Typical

Guaranteed Specifications*

(From -55°C to +85°C)

Frequency Range		5-1000 MHz
Insertion Loss	5-500 MHz	0.5 dB Max
(Less coupling)	500-1000 MHz	1.0 dB Max
Isolation	5-500 MHz 500-1000 MHz	25 dB Min 20 dB Min
Amplitude Balance	5-1000 MHz	0.2 dB Max
Phase Balance	5-500 MHz 500-1000 MHz	2° Max 3° Max
VSWR (All Ports)	10-500 MHz 5-1000 MHz	1.3:1 Max 1.5:1 Max

Operating Characteristics

Impedance	50 Ohms Nominal
Maximum Power Rating or Input Power	1 Watt Max
Internal Load Dissipation	0.05 Watt Max
Package Type	Flatpack (FP-2)
(Se	e page 474 for physical dimensions.)

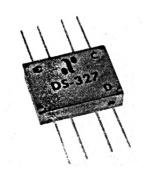
Environmental

These units are designed to meet the environmental and screening requirements of Table 1A, page 496 of the Adams-Russell catalog.

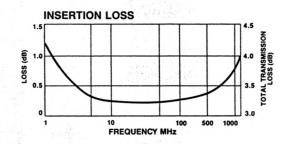
Pin Configuration

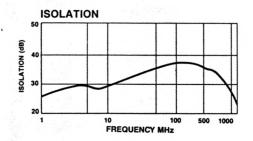
Σ; P1, Output 'C'; P4, Output 'D'; P8

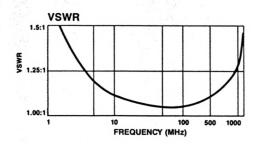
Case and all other pins ground.



Typical Performance







Ordering Information

Model No.	Part No.	Connectors	Unit Price (5-9 Units)
DS-327	6699	Pin	\$58

Delivery is from stock.



Make the Connection...

Adams Russell

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COMPONENTS GROUP

^{*}All specifications apply with 50 ohm source and load impedance.

HIGH FREQUENCY QUADRATURE HYBRID 500-1000 MHz

Octave Bandwidth
Low VSWR — 1.2:1 Typical
Miniature Size — ½" x ¾" Flatpack

Guaranteed Specifications*

(From -55°C to +85°C)

Frequency Range	500-1000 MHz
Insertion Loss (Less coupling)	0.3 dB Max Avg**
Isolation	20 dB Min
Amplitude Balance	1.0 dB Max
VSWR	1.2:1 Max
Deviation from Quadrature	2° Max

Operating Characteristics

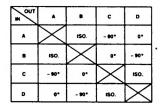
Impedance	50 Ohms Nominal
Input Power	25 Watts Max @ 25.°C;
	Derated to 1 Watt @ 85°C
Package Type	Flatpack (FP-2)
	(See page 474 for physical dimensions.)

Environmental

These units are designed to meet the environmental and screening requirements of Table 1A, page 496 of the Adams-Russell catalog.

Pin ConfigurationA; P1, B; P4, C; P8, D; P5. All other pins are ground.

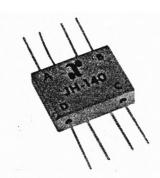
Phasing Diagram



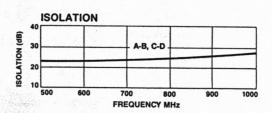
Ordering Information

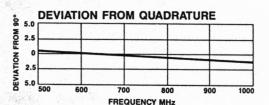
Model No.	Part No.	Connectors	Unit Price (5-9 Units)
JH-140	6619	Pin	\$76

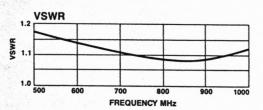
Delivery is from stock.

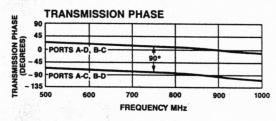


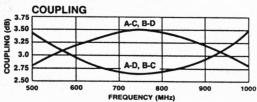
Typical Performance













Make the Connection . . .

Adams Russell

80 Cambridge Street, Burlington, MA 01803 Fax (617) 273-1921

For Ordering Information, Call (617) 273-3333

^{*}All specifications apply with 50 ohm source and load impedance.

^{**}Average of coupled outputs less 3 dB.



DI CMOS **Protected Analog Switches**

AD7510DI/AD7511DI/AD7512DI

FEATURES Latch-Proof

Overvoltage-Proof: ±25V Low Ron: 75 \Omega Low Dissipation: 3mW TTL/CMOS Direct Interface Silicon-Nitride Passivated **Monolithic Dielectrically Isolated CMOS** Standard 14-/16-Pin DIPs and 20-Terminal Surface Mount Packages

GENERAL DESCRIPTION

The AD7510DI, AD7511DI and AD7512DI are a family of latch proof dielectrically isolated CMOS switches featuring overvoltage protection up to ±25V above the power supplies. These benefits are obtained without sacrificing the low "ON" resistance (75Ω) or low leakage current (500pA), the main features of an analog switch.

The AD7510DI and AD7511DI consist of four independent SPST analog switches packaged in either a 16-pin DIP or a 20terminal surface mount package. They differ only in that the digital control logic is inverted. The AD7512DI has two independent SPDT switches packaged either in a 14-pin DIP or a 20-terminal surface mount package.

Very low power dissipation, overvoltage protection and TTL/ CMOS direct interfacing are achieved by combining a unique circuit design and a dielectrically isolated CMOS process. Silicon nitride passivation ensures long term stability while monolithic construction provides reliability.

ORDERING INFORMATION1

Temperature Range and Package²

Temperature Kange and Package							
- 25°C to + 85°C	−55°C to +125°C						
Hermetic ⁴	Hermetic ⁴						
AD7510DIJQ	AD7510DISQ						
AD7510DIKQ	AD7510DITQ						
AD7511DIJQ	AD7511DITQ						
AD7511DIKQ	AD7512DISQ						
AD7512DIJQ	AD7512DITQ						
AD7512DIKQ							
	LCCC6(E-20A)						
	AD7510DISE						
	AD7511DISE						
	AD7511DITE						
	AD7512DISE						
	AD7512DITE						
	-25°C to +85°C Hermetic ⁴ AD7510DIJQ AD7510DIKQ AD7511DIJQ AD7511DIKQ AD7512DIJQ						

NOTES

To order MIL-STD-883, Class B processed parts, add/883B to part

number. Contact your local sales office for military data sheet

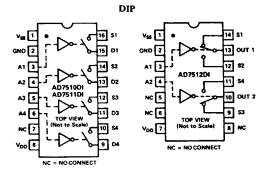
See Section 14 for package outline information.
For AD7510DIJN/KN and AD7511DIJN/KN package outline N-16;

tor AD7512DIJN/KN package outline N-14. For AD7510DIJQ/KQ/SQ and AD7511DIJQ/KQ/SQ/TQ package outline Q-16;

for AD7512DIJQ/KQ/SQ/TQ package outline Q-14. PLCC: Plastic Leaded Chip Carrier.

61.CCC: Leadless Ceramic Chip Carrier

AD7510DI/AD7511DI/AD7512DI FUNCTIONAL BLOCK DIAGRAMS AND PIN CONFIGURATIONS



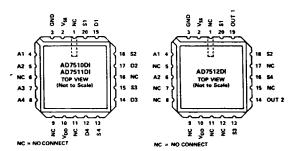
CONTROL LOGIC

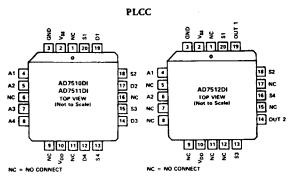
AD7510DI: Switch "ON" for Address "HIGH" AD7511DI: Switch "ON" for Address "LOW"

AD7512DI: Address "HIGH" makes \$1 to Out 1 and \$3 to

PIN CONFIGURATIONS

LCCC

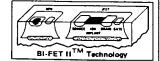






Operational Amplifiers/Buffers

LF411A/LF411 Low Offset, Low Drift JFET Input Operational Amplifier



General Description

These devices are low cost, high speed, JFET input operational amplifiers with very low input offset voltage and guaranteed input offset voltage drift. They require low supply current yet maintain a large gain bandwidth product and fast slew rate. In addition, well matched high voltage JFET input devices provide very low input bias and offset currents. The LF411 is pin compatible with the standard LM741 allowing designers to immediately upgrade the overall performance of existing designs.

These amplifiers may be used in applications such as high speed integrators, fast DIA converters, sample and hold circuits and many other circuits requiring low input offset voltage and drift, low input bias current, high input impedance, high slew rate and wide bandwidth.

Features

■ Internally trimmed offset voltage	0.5 mV (max)
■ Input offset voltage drift	10 μV/°C (max)
Low input bias current	50 pA
Low input noise current	0.01 pA/√Hz
■ Wide gain bandwidth	3 MHz (min)
■ High slew rate	10V/µs (min)
■ Low supply current	1.8 mA
■ High input impedance	10 ¹² Ω
Low total harmonic distortion $A_V = 10$, $R_L = 10k$, $V_O = 20$ Vp-p, BW = 20 Hz-20 k	< 0.02%
Low 1/f noise corner	50 Hz

Low 1/f noise corner
Fast settling time to 0.01%

2 45

Typical Connection

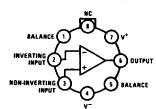
Ordering Information

LF411XYZ

- X indicates electrical grade
- Y indicates temperature range "M" for military, "C" for commercial
- Z indicates package type "H" or "N"

Connection Diagrams

LF411AMH/LF411MH, LF411ACH/LF411CH Metal Can Package

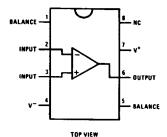


TOP VIEW

Note. Pin 4 connected to case.

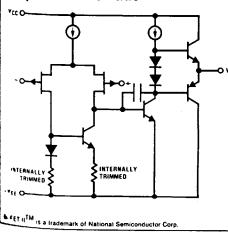
Order Number LF411AMH, LF411MH, LF411ACH or LF411CH See NS Package H08B

> LF411ACN, LF411CN Dual-In-Line Package



Order Number LF411ACN or LF411CN See NS Package N08A

Simplified Schematic



3-5

National Semiconductor

Operational Amplifiers/Buffers

LH0022/LH0022C High Performance FET Op Amp LH0042/LH0042C Low Cost FET Op Amp LH0052/LH0052C Precision FET Op Amp

General Description

The LH0022/LH0042/LH0052 are a family of FET input operational amplifiers with very closely matched input characteristics, very high input impedance, and ultra-low input currents with no compromise in noise, common mode rejection ratio, open loop gain, or slew rate. The internally laser nulled LH0052 offers 500 microvolts maximum offset and 5 µV/°C offset drift. Input offset current is less than 500 femtoamps at room temperature and 500 pA maximum at 125°C. The LH0022 and LH0042 are not internally nulled but offer comparable matching characteristics. All devices in the family are internally compensated and are free of latch-up and unusual oscillation problems. The devices may be offset nulled with a single 10k trimpot with neglible effect in CMRR.

The LH0022, LH0042 and LH0052 are specified for operation over the -55°C to +125°C military temperature range. The LH0022C, LH0042C and LH0052C are specified for operation over the -25°C to +85°C temperature range.

Features

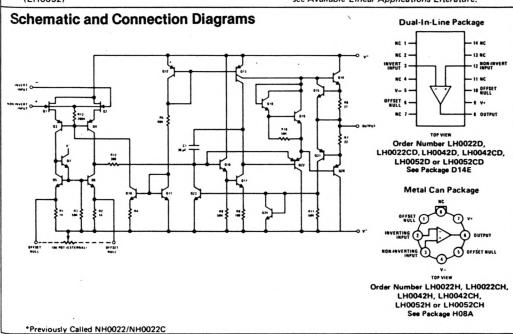
 Low input offset current –500 femtoamps max. (LH0052)

- Low input offset drift 5µV/°C max (LH0052)
- Low input offset voltage 100 microvolts-typ.
- High open loop gain 100 dB typ.
- Excellent slew rate 3.0 V/µs typ.
- Internal 6 dB/octave frequency compensation
- Pin compatible with standard IC op amps (TO-5 package)

The LH0022/LH0042/LH0052 family of IC op amps are intended to fulfill a wide variety of applications for process control, medical instrumentation, and other systems requiring very low input currents and tightly matched input offsets. The LH0052 is particularly suited for long term high accuracy integrators and high accuracy sample and hold buffer amplifiers. The LH0022 and LH0042 provide low cost high performance for such applications as electrometer and photocell amplification, pico-ammeters, and high input impedance buffers.

Special electrical parameter selection and custom built circuits are available on special request.

For additional application information and information on other National operational amplifiers, see Available Linear Applications Literature.



3-311

Voltage Comparators

LM193/LM293/LM393, LM193A/LM293A/LM393A, LM2903 Low Power Low Offset Voltage Dual Comparators

General Description

The LM193 series consists of two independent precision voltage comparators with an offset voltage specification as low as 2.0 mV max for two comparators which were designed specifically to operate from a single power supply over a wide range of voltages. Operation from split power supplies is also possible and the low power supply current drain is independent of the magnitude of the power supply voltage. These comparators also have a unique characteristic in that the input commonde voltage range includes ground, even though operated from a single power supply voltage.

Application areas include limit comparators, simple analog to digital converters; pulse, squarewave and time delay generators; wide range VCO; MOS clock timers; multivibrators and high voltage digital logic gates. The LM193 series was designed to directly interface with TTL and CMOS. When operated from both plus and minus power supplies, the LM193 series will directly interface with MOS logic where their low power drain is a distinct advantage over standard comparators.

Advantages

- High precision comparators
- Reduced V_{OS} drift over temperature

- Eliminates need for dual supplies
- Allows sensing near ground
- Compatible with all forms of logic
- Power drain suitable for battery operation

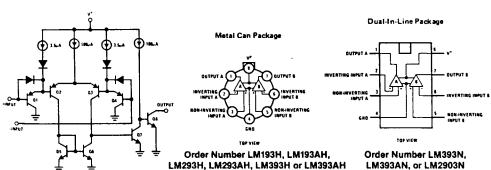
Features

- Wide single supply

 Voltage range
 or dual supplies

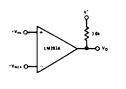
 2.0 V_{DC} to 36 V_{DC}
 ±1.0 V_{DC} to ±18 V_{DC}
- Very low supply current drain (0.8 mA)—independent of supply voltage (1.0 mW/comparator at 5.0 V_{DC})
- Low input biasing current 25 nA
 Low input offset current ±5 nA
 and maximum offset voltage ±3 mV
- Input common-mode voltage range includes ground
- Differential input voltage range equal to the power supply voltage
- Low output 250 mV at 4 mA saturation voltage
- Output voltage compatible with TTL, DTL, ECL, MOS and CMOS logic systems

Schematic and Connection Diagrams



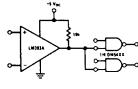
See NS Package H08C

Typical Applications $(V^+ = 5.0 V_{DC})$



Basic Comparator

Driving CMOS



See NS Package N08B

Driving TTL

MC4344 • MC4044

R

10

3 c

Phase-Freq Detector

#1

Phase-Freq Detector



ISSUE A

The MC4344/4044 consists of two digital phase detectors, a charge pump, and an amplifier. In combination with a voltage controlled multivibrator (such as the MC4324/4024 or MC1648), it is useful in a broad range of phase-locked loop applications. The circuit accepts MTTL waveforms at the R and V inputs and generates an error voltage that is proportional to the frequency and/or phase difference of the input signals. Phase detector #1 is intended for use in systems requiring zero frequency and phase difference at lock. Phase detector #2 is used if quadrature lock is desired. Phase detector #2 can also be used to indicate that the main loop, utilizing phase detector #1, is out of lock.



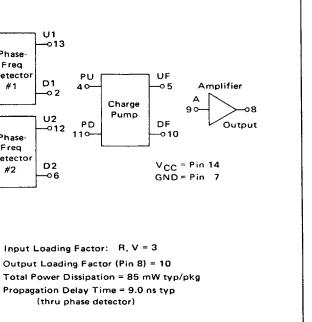
F SUFFIX CERAMIC PACKAGE **CASE 607** (TO-86)

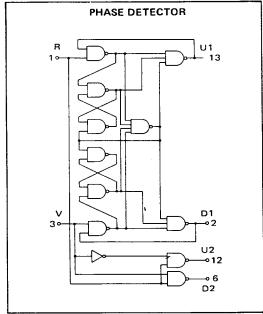


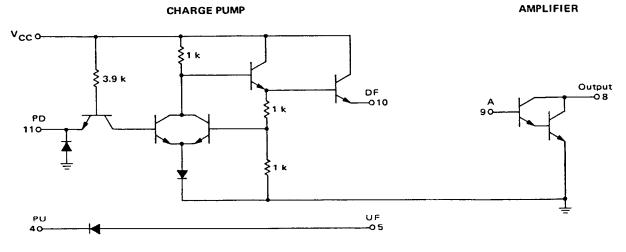
CERAMIC PACKAGE **CASE 632** (TO-116)



P SUFFIX PLASTIC PACKAGE **CASE 646** (TO-116) MC4044 only







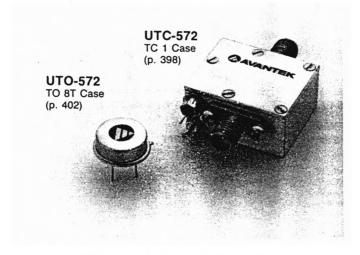
UTO-572

Reverse Isolation Amplifiers 50-500 MHz



FEATURES

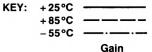
- · High Reverse Isolation
- Wideband
- Low VSWR

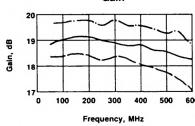


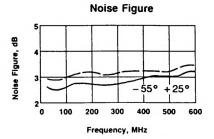
ELECTRICAL SPECIFICATIONS (Measured in a 50-ohm system @ +15 VDC nominal unless otherwise noted)

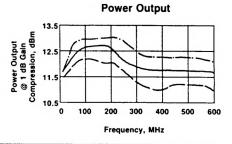
		Typical	Guaranteed Specifications		
Symbol Characteristic	T _C = 25°C	T _C = 0°-50°C	$T_{C} = -55^{\circ}- +85^{\circ}C$	Unit	
BW	Frequency Range	50-500	50-500	50-500	MHz
GP	Small Signal Gain	18.5	18.0 Min.	17.0 Min.	dB
_	Gain Flatness	±0.3	± 0.5 Max.	± 1.0 Max.	dB
NF	Noise Figure	3.0	3.5 Max.	3.7 Max.	dB
	Reverse Isolation	50	45	45	dB
P _{1dB}	Power Output @ + 1 dB Compression	+12.0	+11.0 Min.	+ 10.0 Min.	dBm
_	Input VSWR	1.5:1	2.0:1 Max.	2.0:1 Max.	_
_	Output VSWR	1.5:1	2.0:1 Max.	2.0:1 Max.	_
IP ₃	Two Tone 3rd Order Intercept Point	+24.0	_	_	dBm
IP ₂	Two Tone 2nd Order Intercept Point	+34.0	_		dBm
HP ₂	One Tone 2nd Harmonic Intercept Point	+42.0	_	-	dBm
ID	DC Current	32	<u> </u>	-	mA

TYPICAL PERFORMANCE OVER TEMPERATURE (@ +15 VDC unless otherwise noted)









MAXIMUM RATINGS

 DC Voltage
 + 17 Volts

 Continuous RF Input Power
 + 13 dBm

 Operating Case Temperature
 -55°C to + 115°C

 Storage Temperature
 -62°C to + 150°C

 "R" Series Burn-In Temperature
 + 115°C

THERMAL CHARACTERISTICS*

*For further information, see High Reliability section.

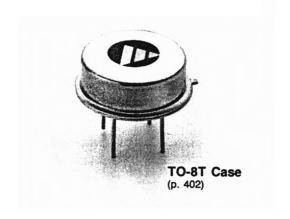
WEIGHT: (typical) UTO-2.1 grams; UTC-21.5 grams

UTM-1055

High Gain Modular Amplifier 10-1000 MHz

FEATURES

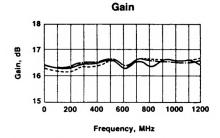
- MODAMP[™] Silicon Monolithic Gain Stages
- Gain: 16.2 dB (Typ.)
- Output Power: +16.5 dBm (Typ.)
- · Increased Reliability

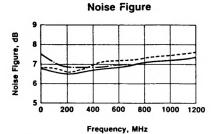


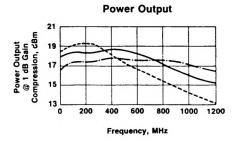
ELECTRICAL SPECIFICATIONS (Measured in a 50-ohm system @ +15 VDC nominal)

		Typical	Guaranteed Specifications		Unit
Symbol Characteristic	T _C = 25°C	$T_C = 0^{\circ}-50^{\circ}C$	$T_{\rm C} = -55^{\circ}- +85^{\circ}{\rm C}$		
BW	Frequency Range	10-1000	10-1000	10-1000	MHz
GP	Small Signal Gain	16.2	15.5 Min.	15.0 Min.	dB
_	Gain Flatness	±0.2	± 0.7 Max.	±0.7 Max.	dB
NF	Noise Figure	7.0	8.0 Max.	8.5 Max.	dB
P 1 dB	Power Output @ + 1 dB Compression	+16.5	+15.0 Min.	+ 12.0 Min.	dBm
_	Input VSWR	1.4:1	1.7:1 Max.	1.7:1 Max.	_
_	Output VSWR	1.2:1	1.7:1 Max.	1.7:1 Max.	_
IP ₃	Two Tone 3rd Order Intercept Point	+29.0	_		dBm
IP ₂	Two Tone 2nd Order Intercept Point	+ 45.0	_	_	dBm
HP ₂	One Tone 2nd Harmonic Intercept Point	+50.0	_	<u> </u>	dBm
I _D	DC Current	135		_	mA

TYPICAL PERFORMANCE OVER TEMPERATURE (@ +15 VDC unless otherwise noted)







MAXIMUM RATINGS

 DC Voltage
 + 17 Volts

 Continuous RF Input Power
 + 20 dBm

 Operating Case Temperature
 -55°C to + 100°C

 Storage Temperature
 -62°C to + 150°C

 "R" Series Burn-In Temperature
 + 85°C

THERMAL CHARACTERISTICS

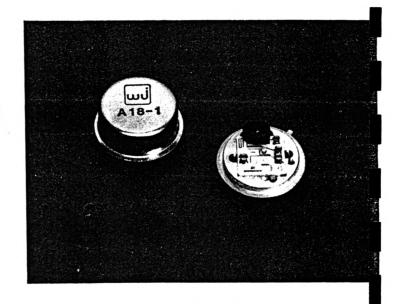
Note 1: Values refer to 1st and 2nd stage transistors respectively.

WEIGHT: (typical) - 2.1 grams

WJ-A18-1

10 TO 1000 MHz TO-8 CASCADABLE AMPLIFIER

- HIGH OUTPUT LEVEL: +16 dBm (TYP.)
- HIGH THIRD ORDER I. P. +30 dBm (TYP.)
- LOW VSWR: 1.5:1 (TYP.)



Specifications*

Characteristics	Typical	Guaranteed 0° - 50° C -54° C $-+89^{\circ}$	
Frequency (Min.)	5-1100 MHz	10-1000 MHz	10-1000 MHz
Small Signal Gain (Min.)	14.7 dB	14.0 dB	13.5 dB
Gain Flatness (Max.)	<±0.3 dB	±0.5 dB	±1.0 dB
Noise Figure (Max.)	3.8 dB	5.0 dB	5.5 dB
Power Output at 1 dB Compression (Min.)	+16.0 dBm	+15.0 dBm	+14.5 dBm
VSWR (Max.) Input/Output	1.5:1	1.8:1	2.0:1
DC Current (Max.) at 15 Volts	44 mA	46 mA	48 mA

^{*}Measured in a 50-ohm system at +15 Vdc Nominal.

Typical Intermodulation Performance at 25°C

Second Order Harmonic Intercept Point	+45 dBm (Typ.)
Second Order Two-Tone Intercept Point	+42 dBm (Typ.)
Third Order Two-Tone Intercept Point	+30 dBm (Typ.)

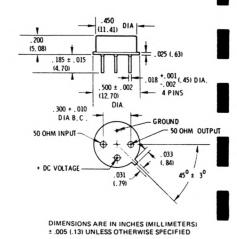
Absolute Maximum Ratings

Absolute Maximum Katings
Storage Temperature
Maximum Case Temperature
Maximum DC Voltage
Maximum Continuous RF Input Power +13 dBm
Maximum Short Term RF Input Power 50 Milliwatts
(1 Minute Max.)
Maximum Peak Power
(3 μsec Max.)
"S" Series Burn-In Temperature (Case)

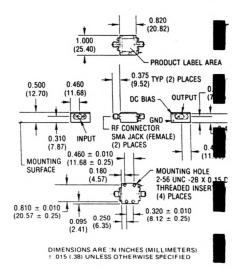
Weight approximately 2.0 grams (0.07 oz.)

Outline Drawings

A18-1



CA18-1

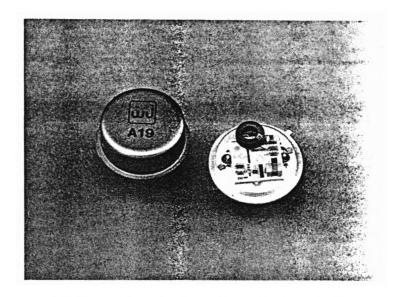


*WJ-CA18-1 is standard WJ-A18-1 installed in miniature SMA connector housing guaranteed over 0° C to 50° C temperature range. See Cascaded Thin Film Amoli

WJ-A19

10 TO 1000 MHz TO-8 CASCADABLE AMPLIFIER

- HIGH OUTPUT POWER: +21 dBm (TYP.)
- HIGH THIRD ORDER I.P.: +34 dBm (TYP.)



Specifications*

Characteristics	Typical	Guaranteed 0°-50°C -54°C - +85°	
Frequency (Min.)	5-1050 MHz	10-1000 MHz	10-1000 MHz
Small Signal Gain (Min.)	7.5 dB	6 dB	5.5 dB
Gain Flatness (Max.)	<±0.3 dB	±1.0 dB	±1.3 dB
Noise Figure (Max.)	9 dB	10.5 dB	11.0 dB
Power Output at 1 dB Compression (Min.)	+21 dBm	+20 dBm	+19 dBm
VSWR (Max.) Input/Output	< 1.8:1	2.2:1	2.2:1
DC Current (Max.) at 15 Volts	100 mA	109 mA	114 mA

^{*}Measured in a 50-ohm system at +15 Vdc Nominal.

Typical Intermodulation Performance at 25°C

Second Order Harmonic Intercept Point	+45 dBm (Typ.)
Second Order Two-Tone Intercept Point	.+40 dBm (Typ.)
Third Order Two-Tone Intercept Point	.+34 dBm (Tvp.)

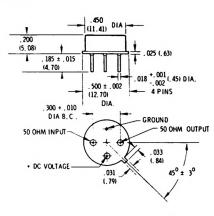
Absolute Maximum Ratings

Storage Temperature
Maximum Case Temperature
Maximum DC Voltage
Maximum Continuous RF Input Power
Maximum Short Term RF Input Power
Maximum Peak Power
"S" Series Burn-In Temperature (Case)

Weight approximately 2.0 grams (0.07 oz.)

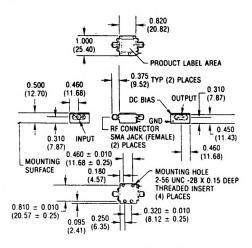
Outline Drawings

A19



DIMENSIONS ARE IN INCHES (MILLIMETERS) ± .005 (.13) UNLESS OTHERWISE SPECIFIED

CA19



DIMENSIONS ARE IN INCHES (MILLIMETERS) ± .015 (.38) UNLESS OTHERWISE SPECIFIED

 $^{\circ}$ WJ CA19 is standard WJ A19 installed in miniature SMA connector housing and guaranteed over 0 $^{\circ}$ C to 50 $^{\circ}$ C temperature range